



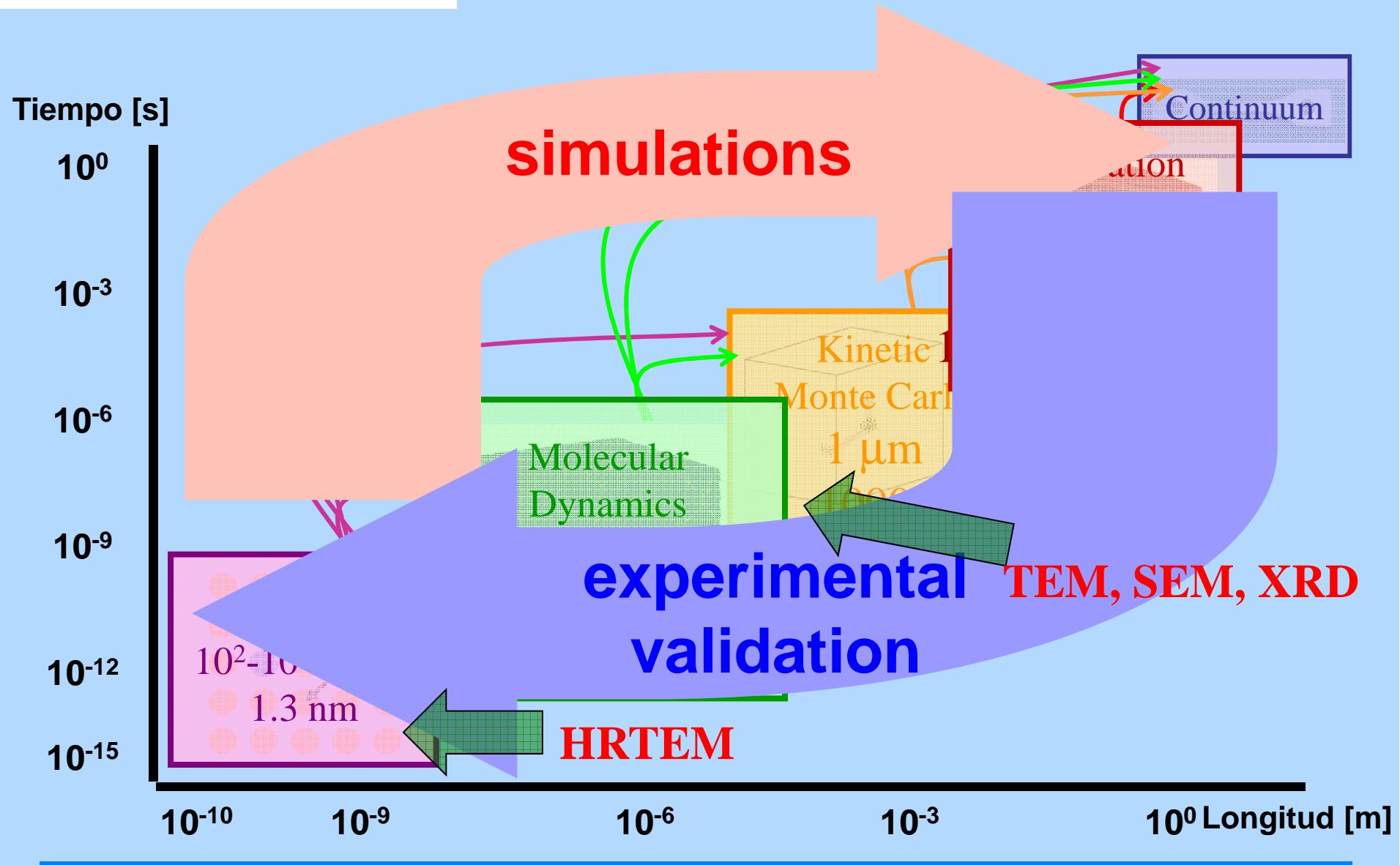
# Métodos de simulación *ab initio* y aplicaciones a materiales bajo irradiación

Roberto Iglesias

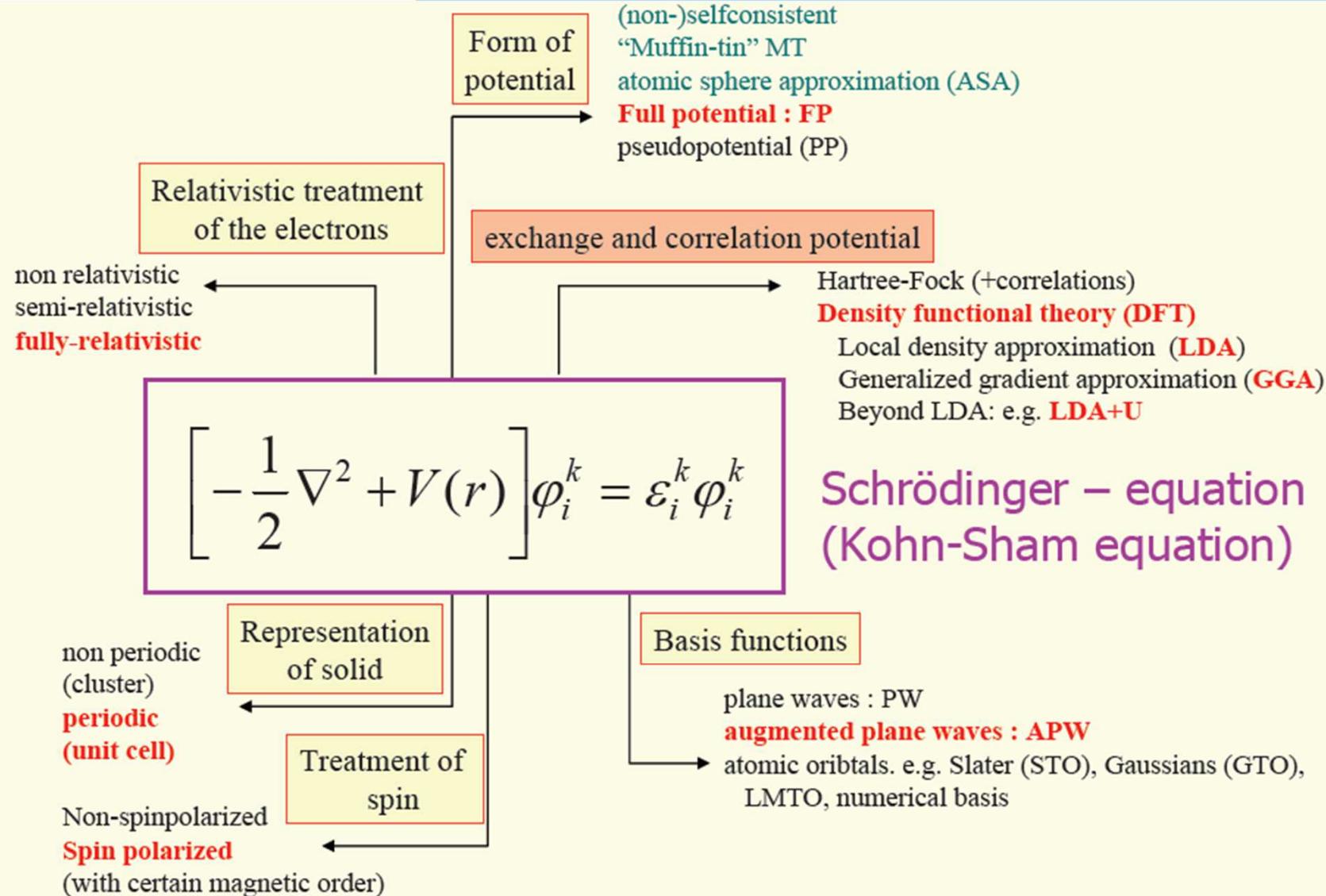
Departamento de Física

Universidad de Oviedo

# MULTISCALE MODELLING PARADIGM



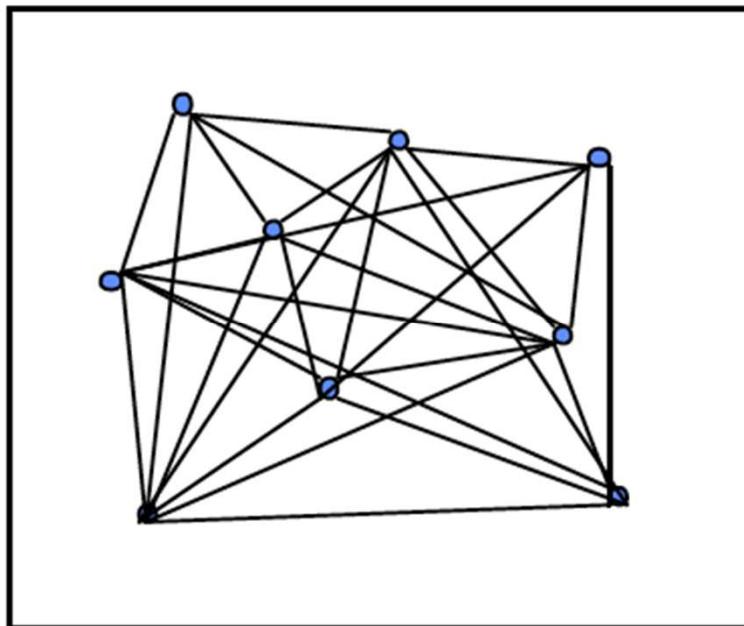
# Solving Schrödinger's equation in solids



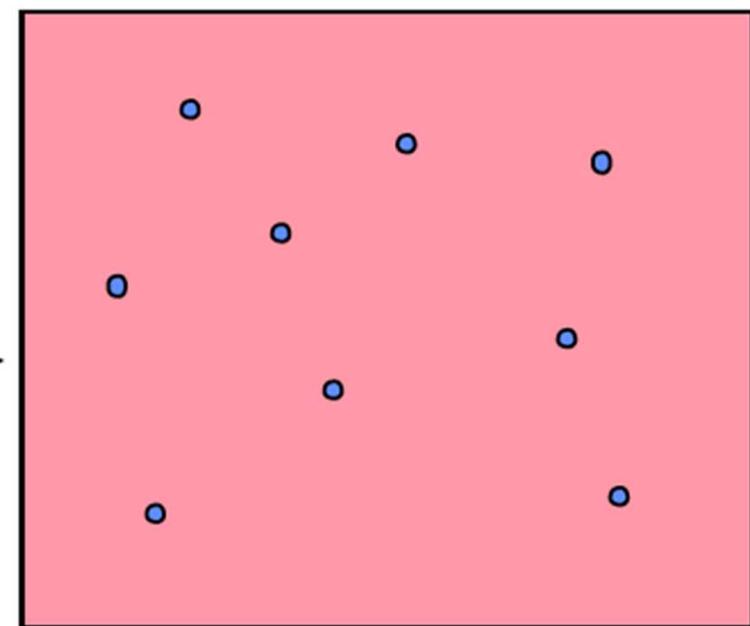
# How does DFT work

$$\sum_{i < j}^N \frac{1}{| \mathbf{r}_i - \mathbf{r}_j |}$$
$$\Psi(\mathbf{r}_1, \mathbf{r}_2, \dots, \mathbf{r}_N)$$

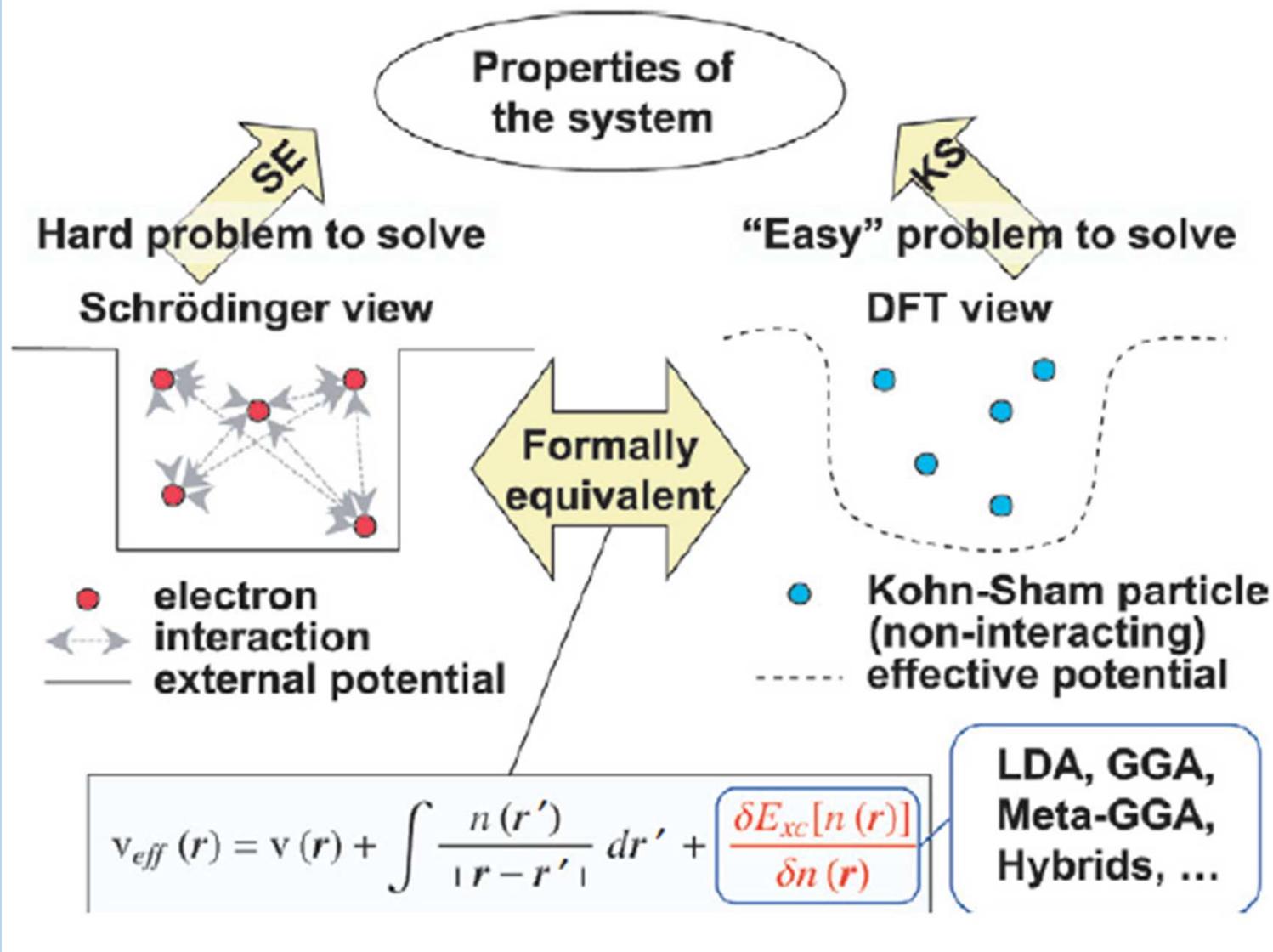
$$v_H(\mathbf{r}) + v_{xc}(\mathbf{r})$$
$$\phi_i(\mathbf{r})$$



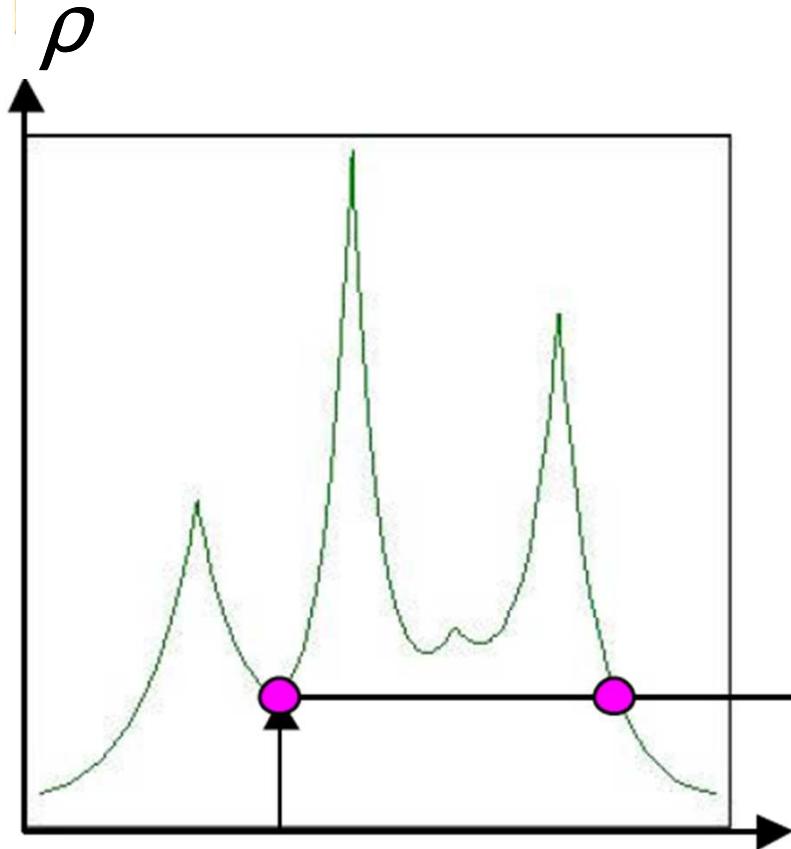
$$E, \rho$$



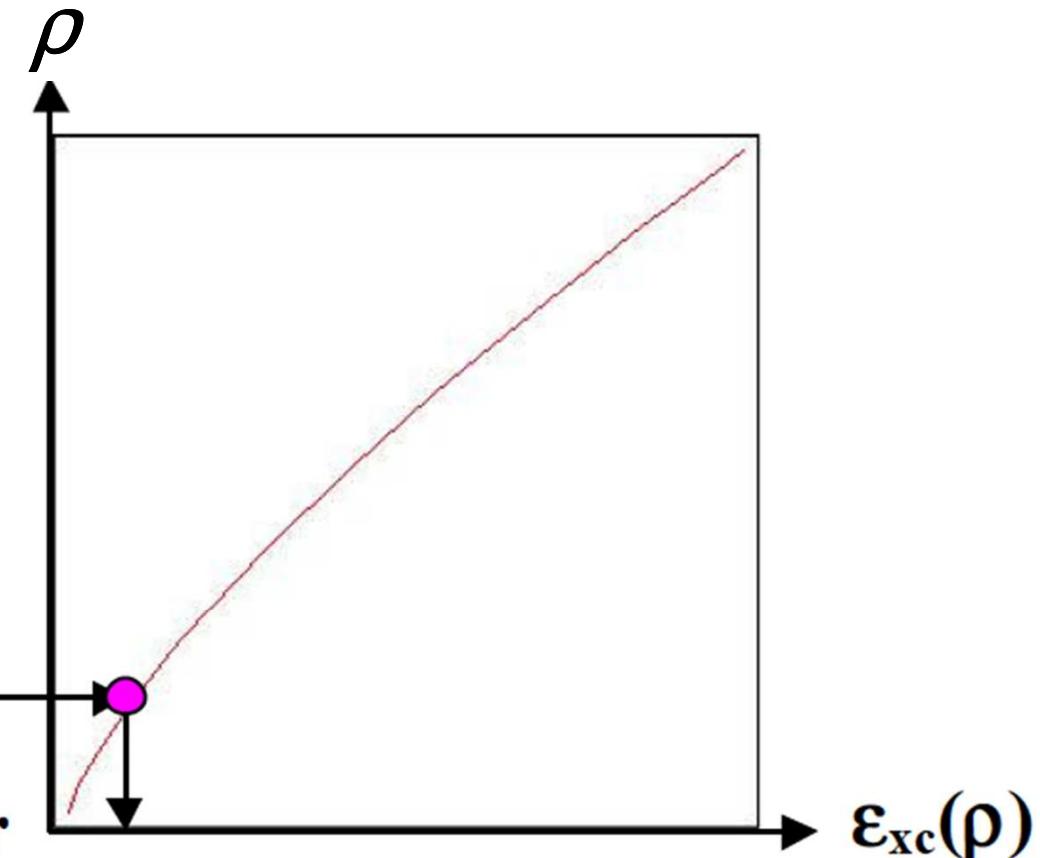
# DFT AND FUNCTIONALS



# LDA approximation



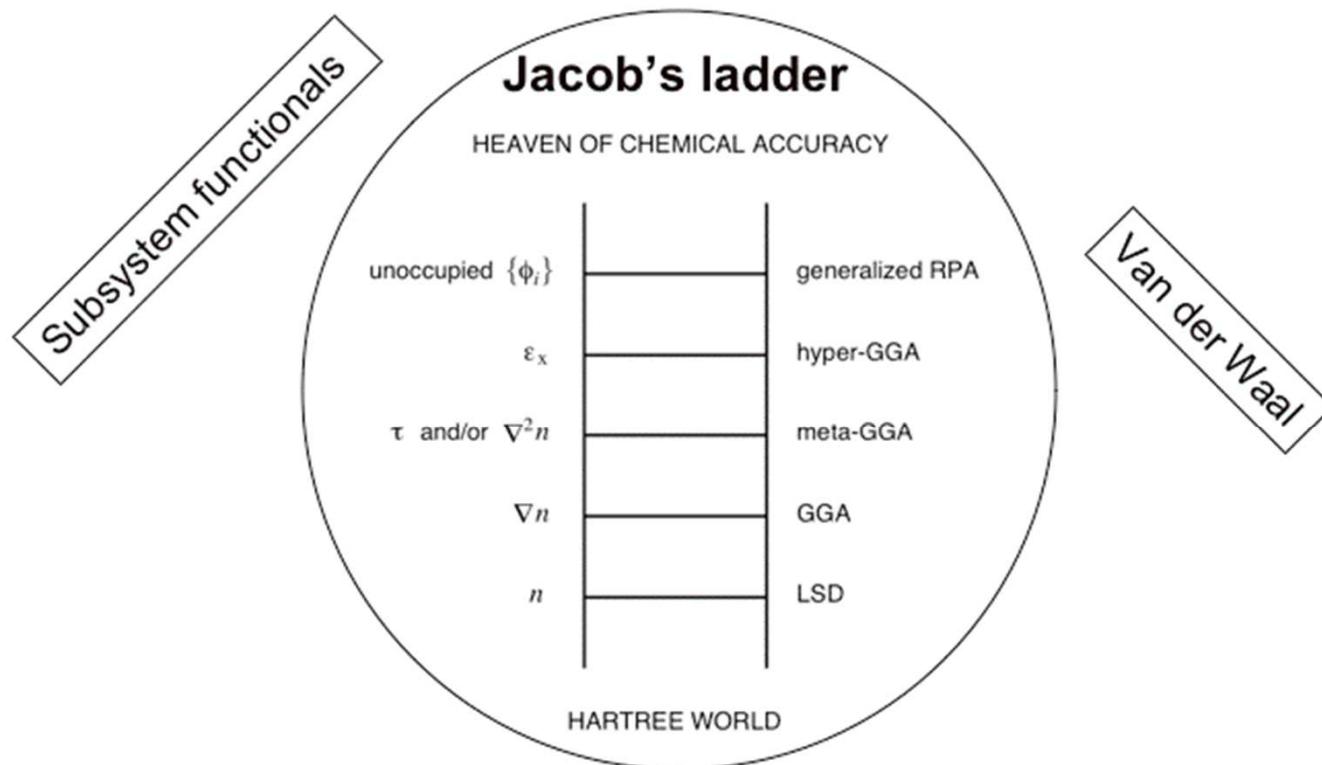
Exchange energy density of  
the inhomogeneous system



Exchange energy density of  
the homogeneous electron gas

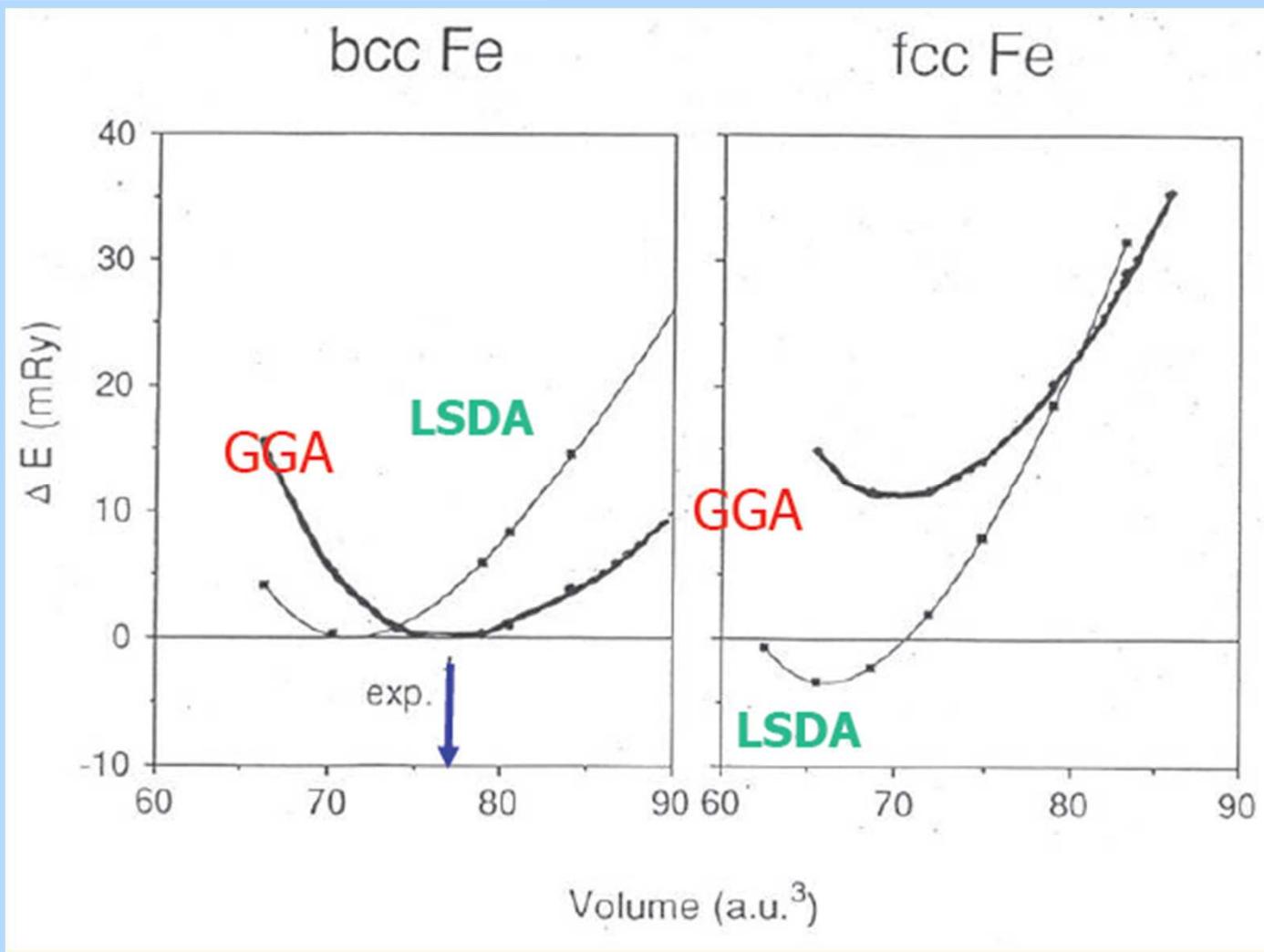
# Accuracy limiting factor

## Hierarchy of functionals



From J.P. Perdew et. al. JCP 123, 062201 (2005).

# DFT ground state of iron



**LSDA**

NM  
fcc  
in contrast to  
experiment

**GGA**

FM  
bcc  
Correct lattice  
constant

**Experiment**

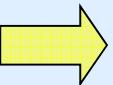
FM  
bcc



# Electronic structure determination

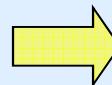
THREE BASIC METHODS:

- Plane waves and grids



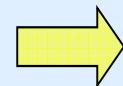
solution of Schr. and Poisson eqs.  
simplicity and speed of FFT  
smooth pseudopotentials

- Localized atomic(-like) orbitals



atomic-like states  
good scaling with size

- Atomic sphere methods



atomic-like features near nucleus  
smooth functions between atoms  
most demanding

Augmented

Linearized

APW  
KKR

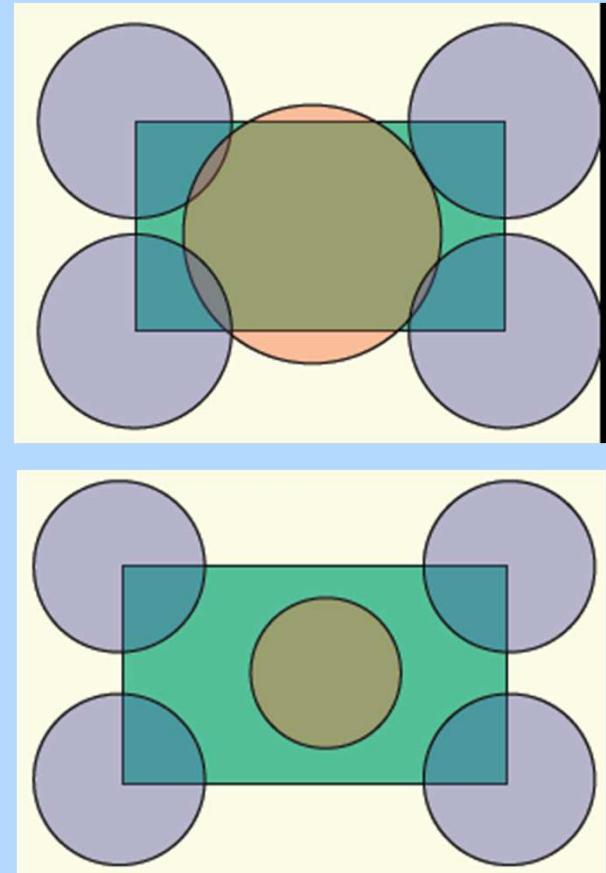
LAPW  
LMTO

most precise  
full-potential

APW+lo  
e.g. TM 3d

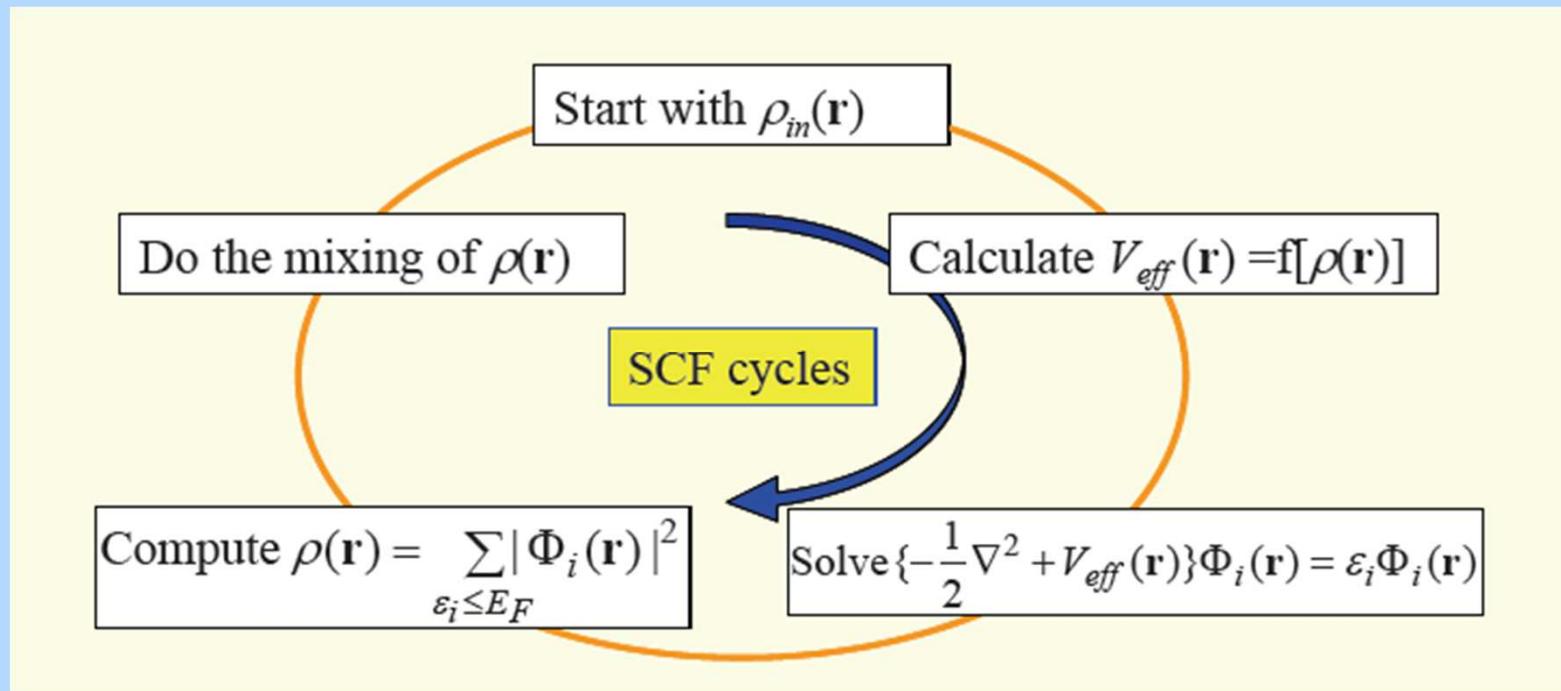
# Shape approximations to “real” potentials

1. Atomic sphere approximation (ASA)
  - overlapping spheres "fill" all volume
  - potential spherically symmetric
  
2. "muffin-tin" approximation (MTA)
  - non-overlapping spheres with spherically symmetric potential +
  - interstitial region with  $V=\text{const.}$
  
3. "full"-potential
  - no shape approximations to  $V$



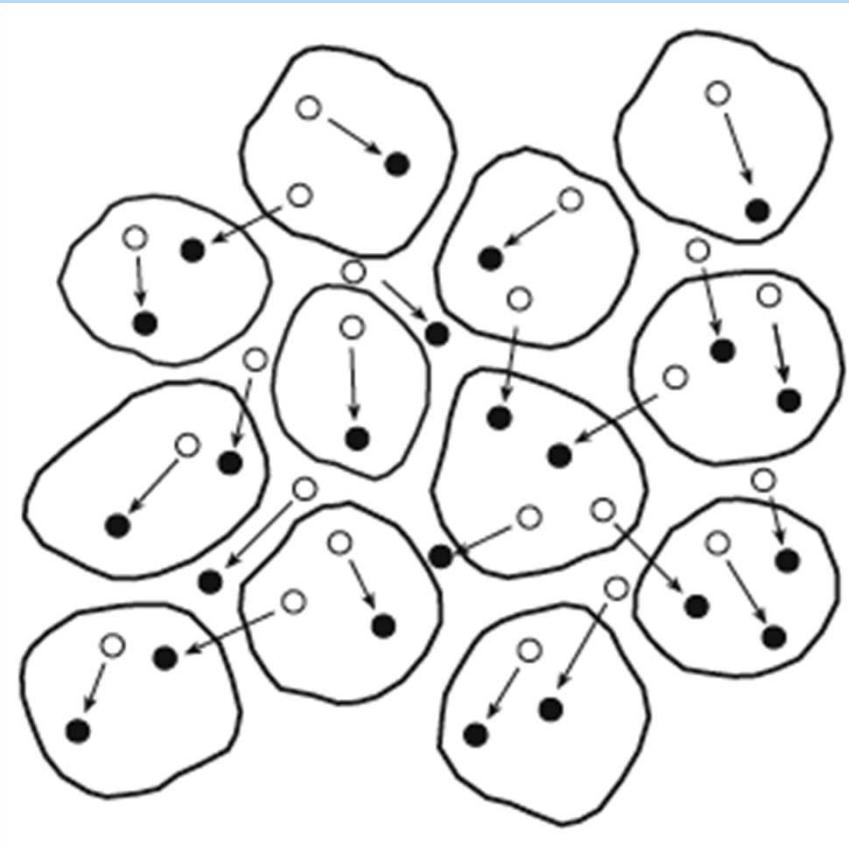
# Self-consistent field (SCF) calculations

- In order to solve  $H\Psi=E\Psi$ , we need to know the potential  $V$
  - For  $V(r)$  we need the electron density  $\rho(r)$
  - The density  $\rho(r)$  can be obtained from  $\Psi(r)^*\Psi(r)$
  - $\Psi(r)$  is unknown before  $H\Psi=E\Psi$  is solved

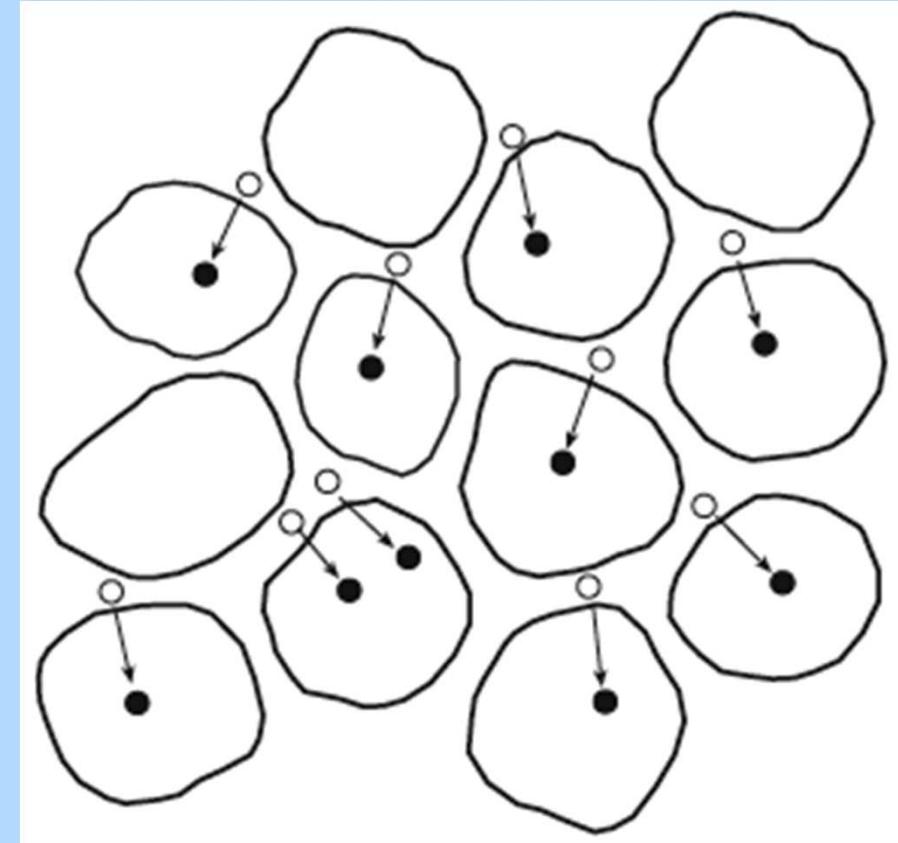


# Irradiated nanocrystalline solids

Ovidko 2005



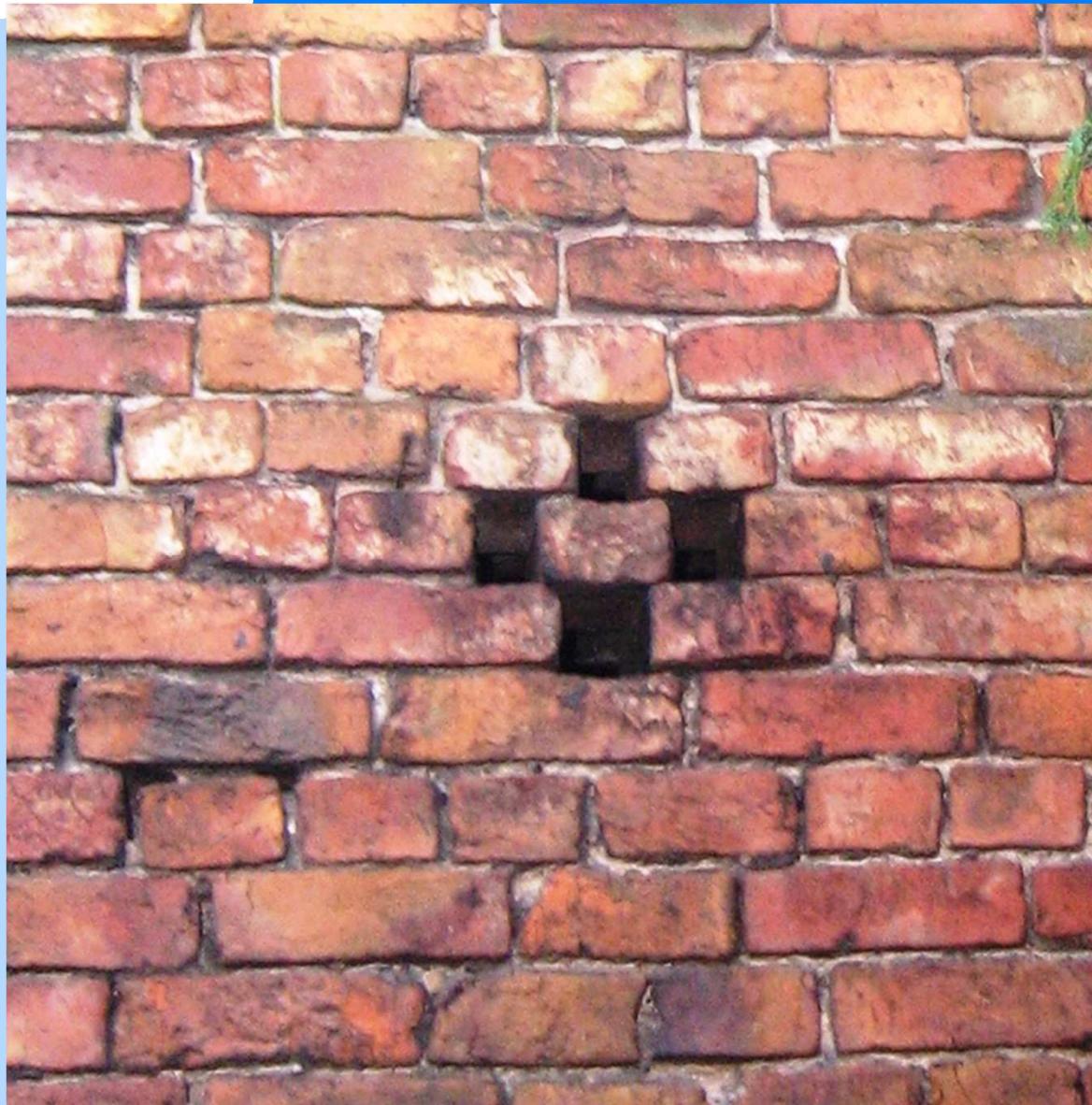
**High irradiation dose**



**Low irradiation dose**

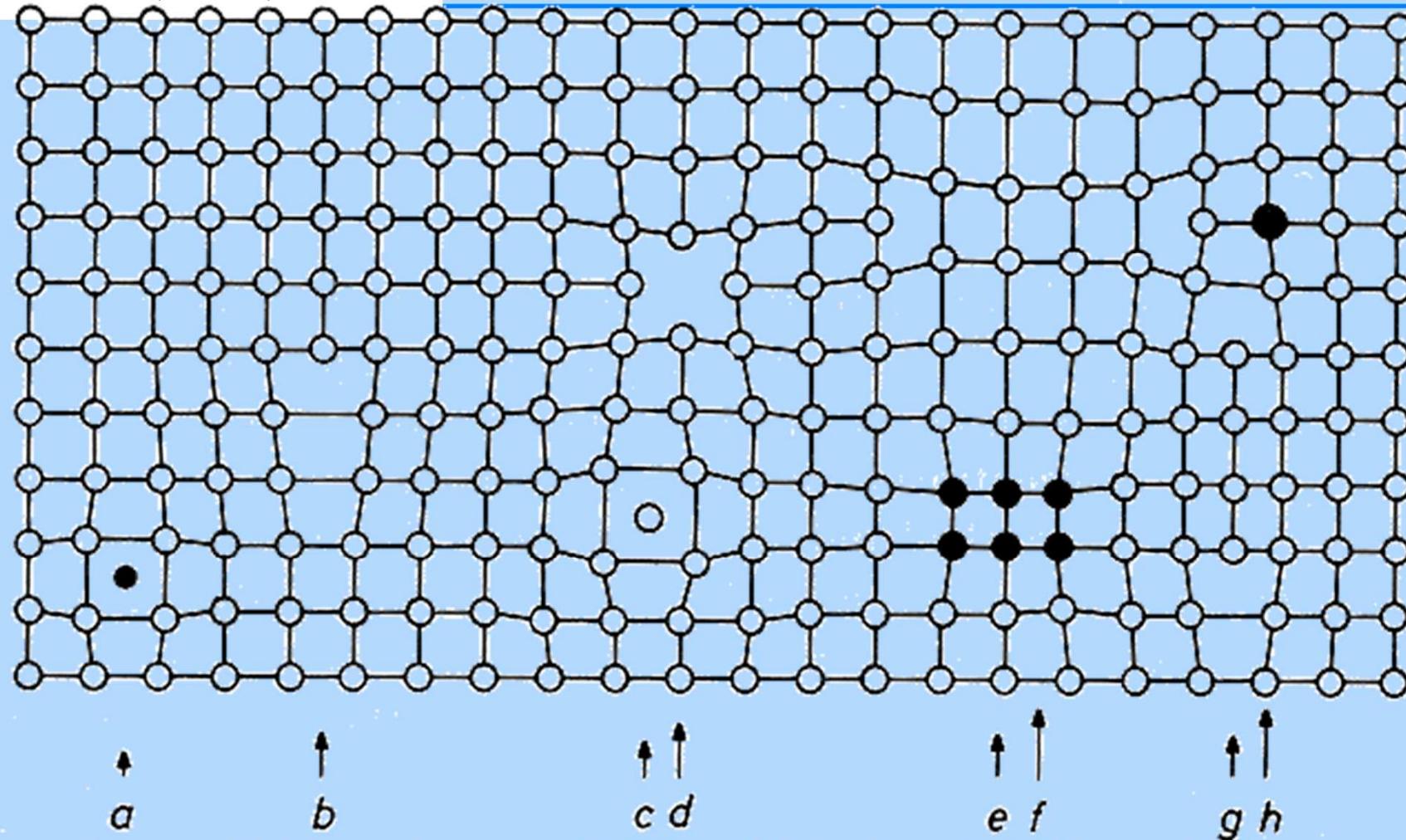


# Tetravacancy

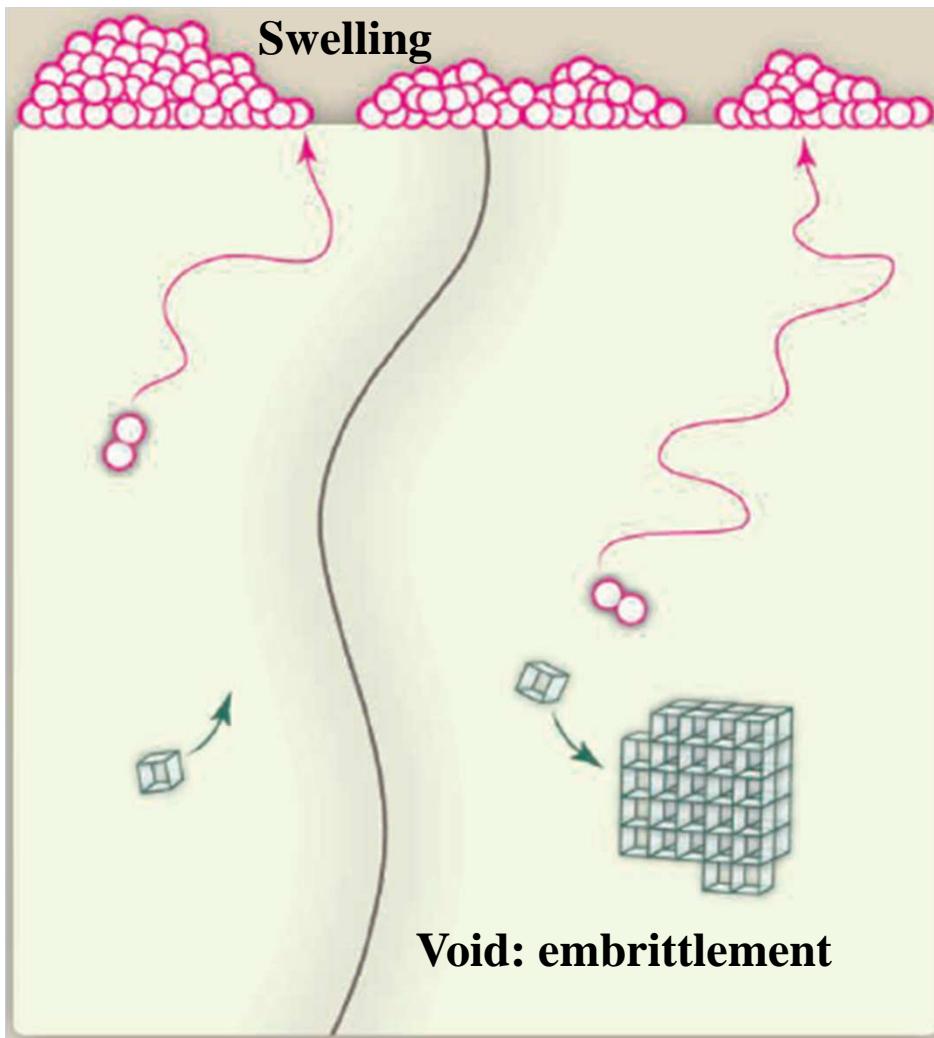




# Defects in crystals



- a) Interstitial impurity atom, b) Edge dislocation, c) Self interstitial atom,
- d) Vacancy, e) Precipitate of impurity atoms, f) Vacancy type dislocation loop, g) Interstitial type dislocation loop, h) Substitutional impurity atom

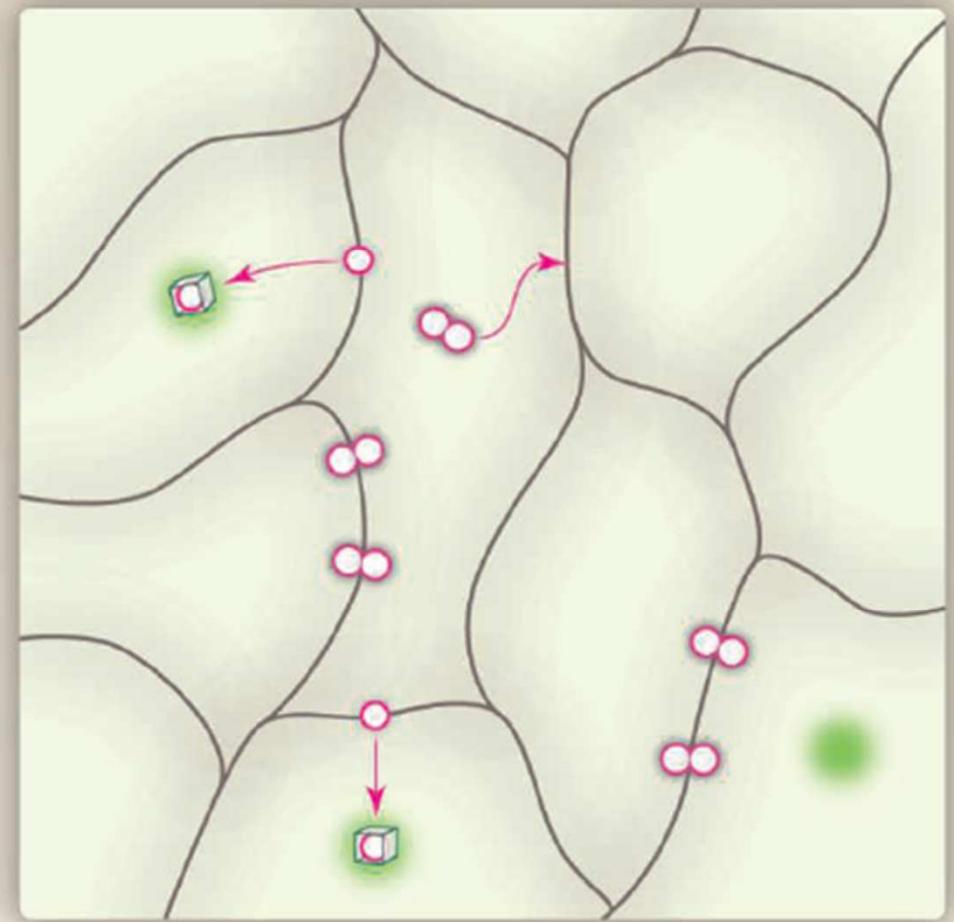


A

CONVENTIONAL MATERIAL

- Self-interstitial
- Vacancy

## Self-healing materials



B

NANOMATERIAL

- Self-interstitial
- Virtual interstitial
- Healed crystal

Ackland 2010

# Irradiated W microstructural evolution

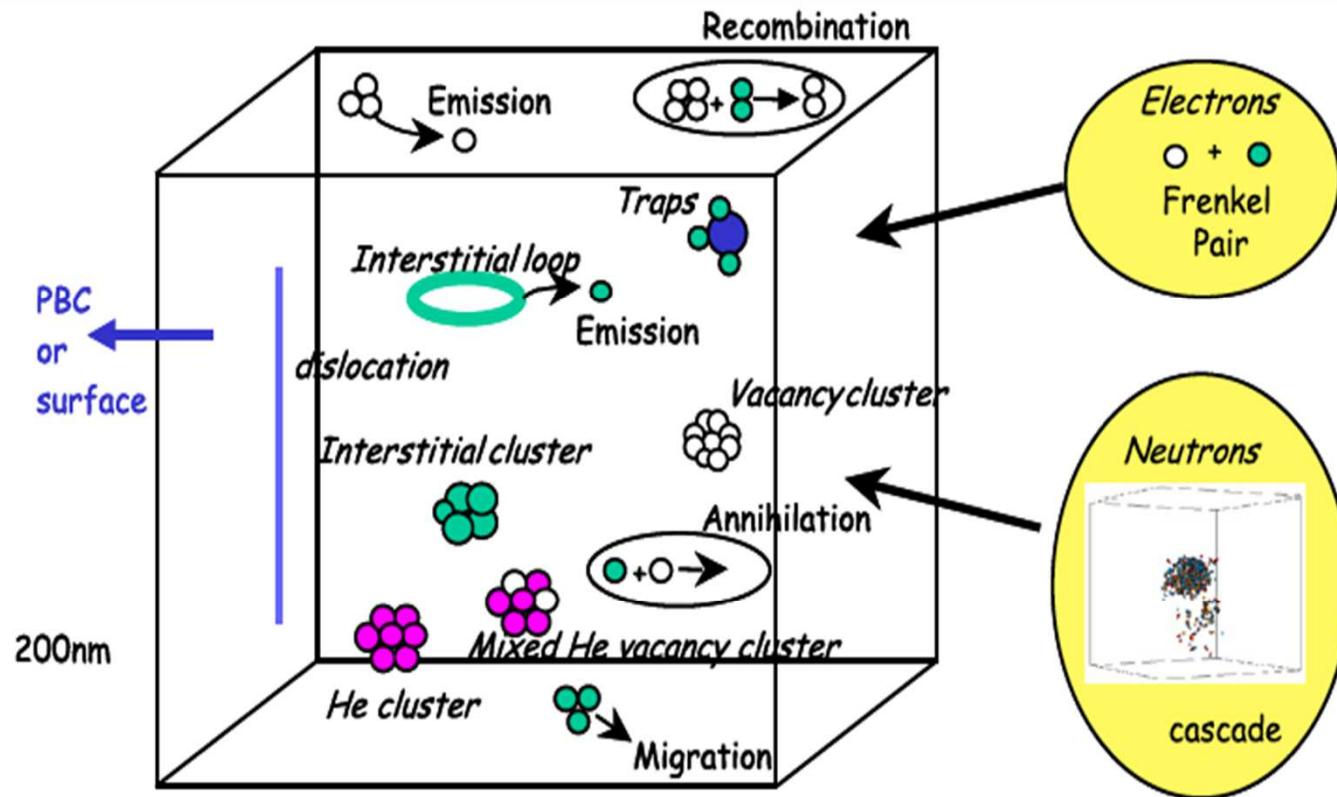
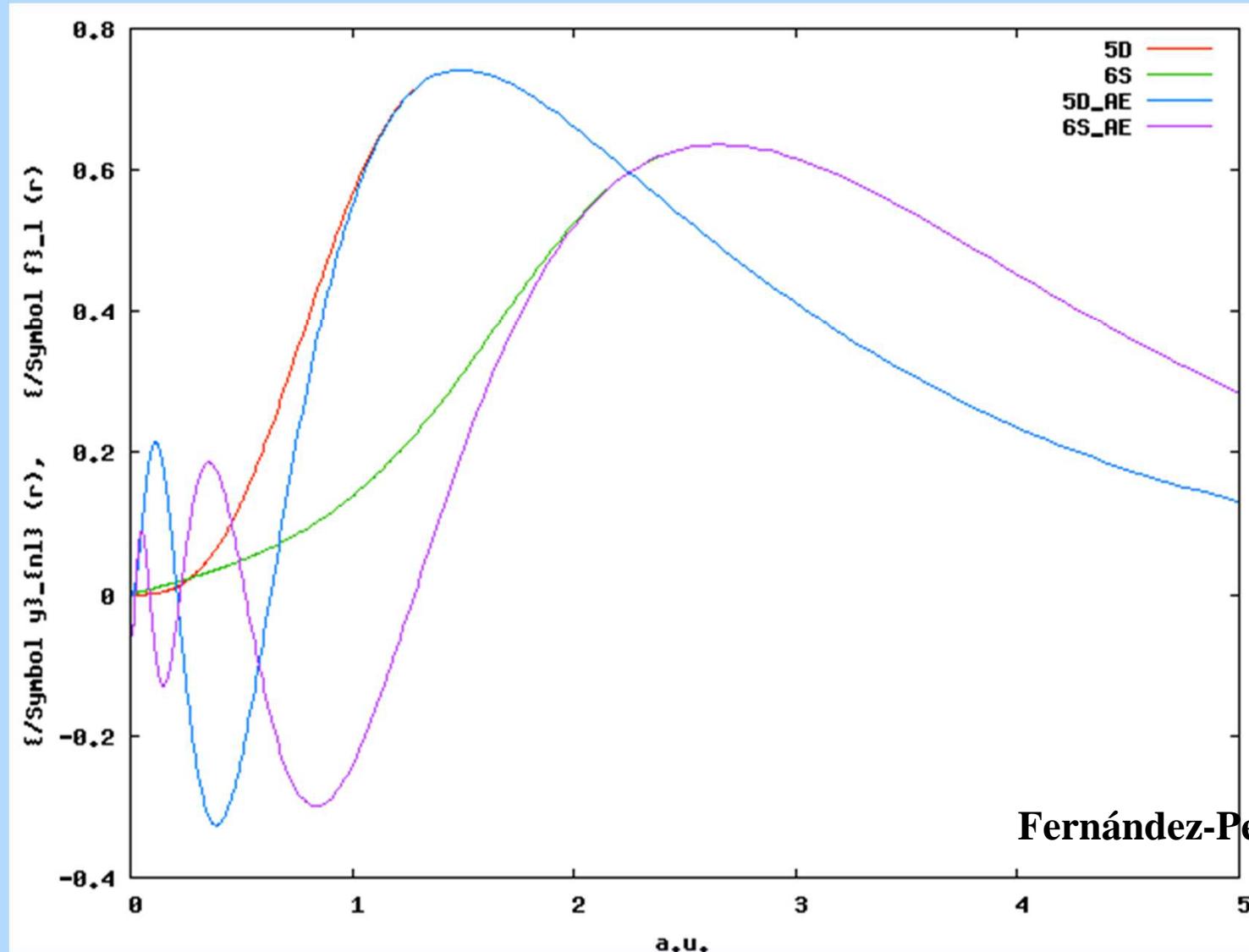
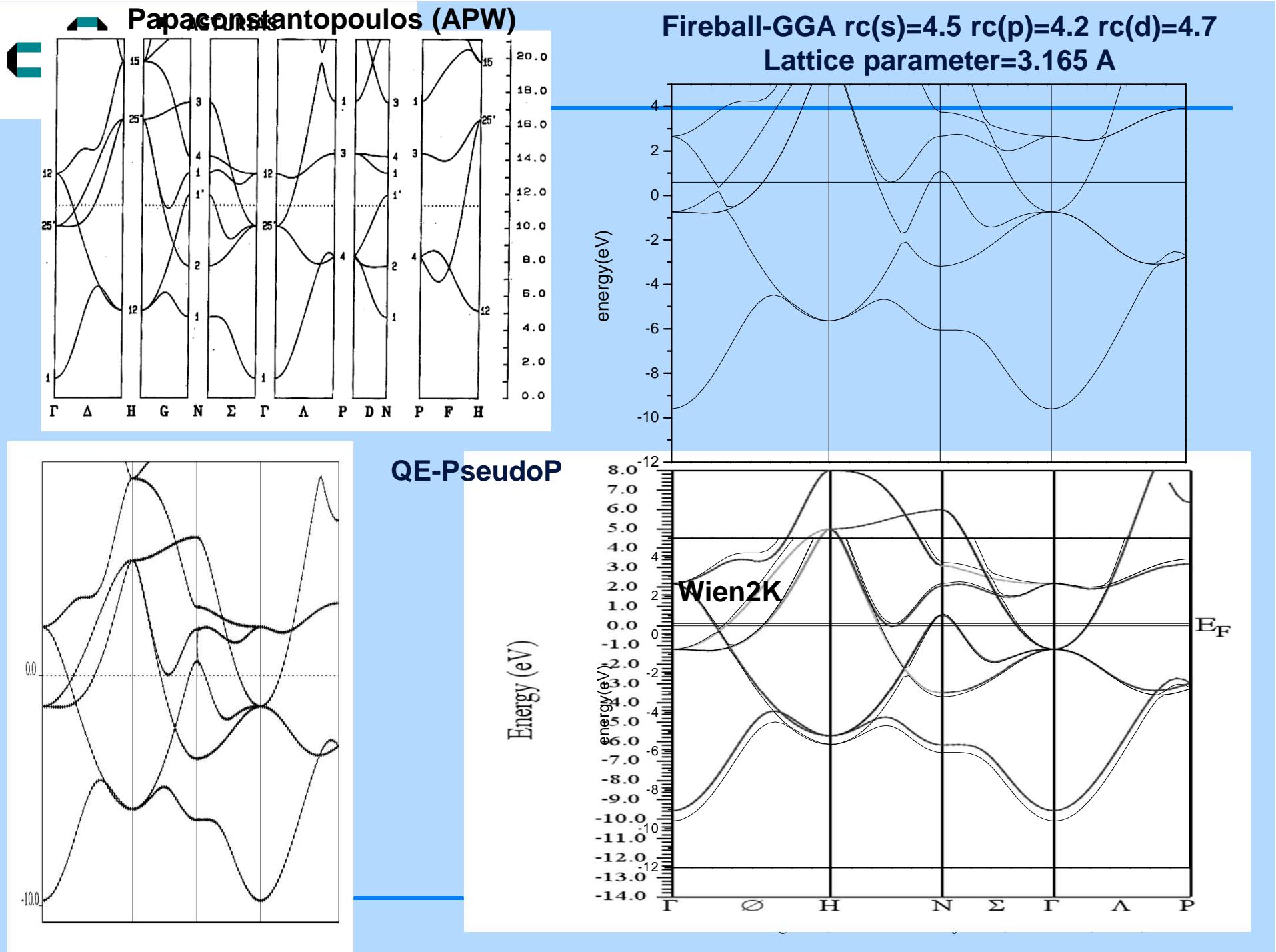


Fig. 1. Summary of the different events: migration, recombination, emission of single entities or trapping as well as electron or neutron irradiations, taking place in an object KMC simulation using the LAKIMOCA code. The white spheres are the vacancies, the green ones, the SIAs; the pink ones represent the helium atoms.

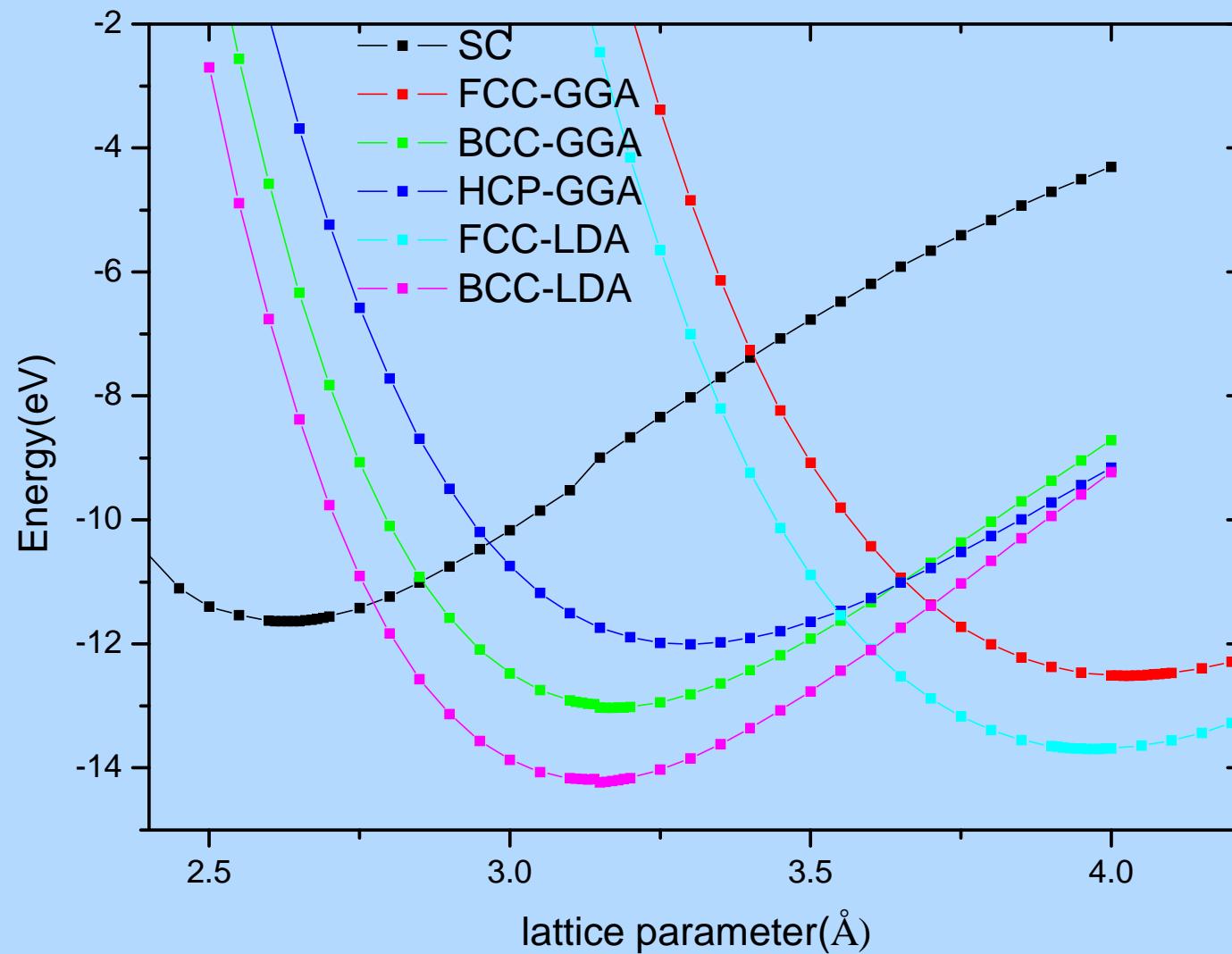
Ab initio data parameterise an OKMC  
model: analyse evolution of defect  
population during He desorption from W

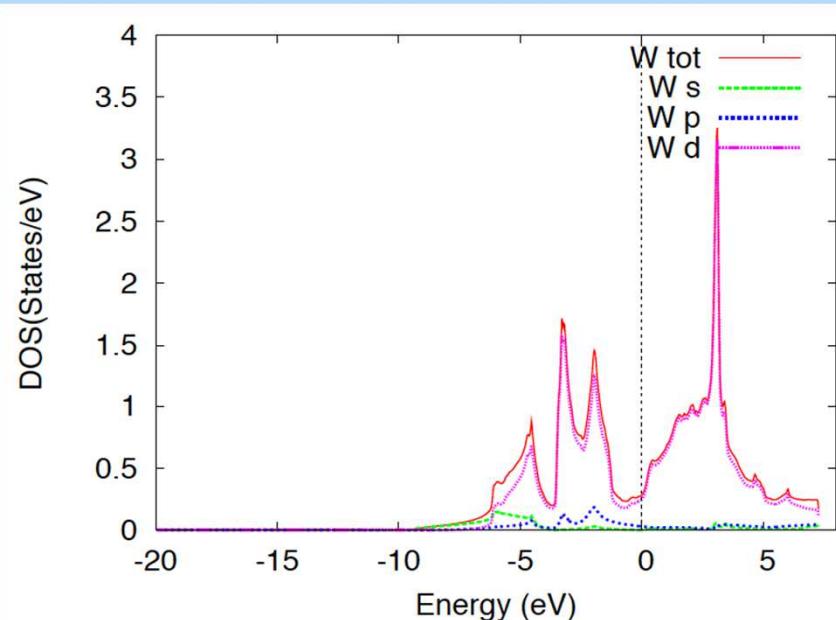
Becquart 2010





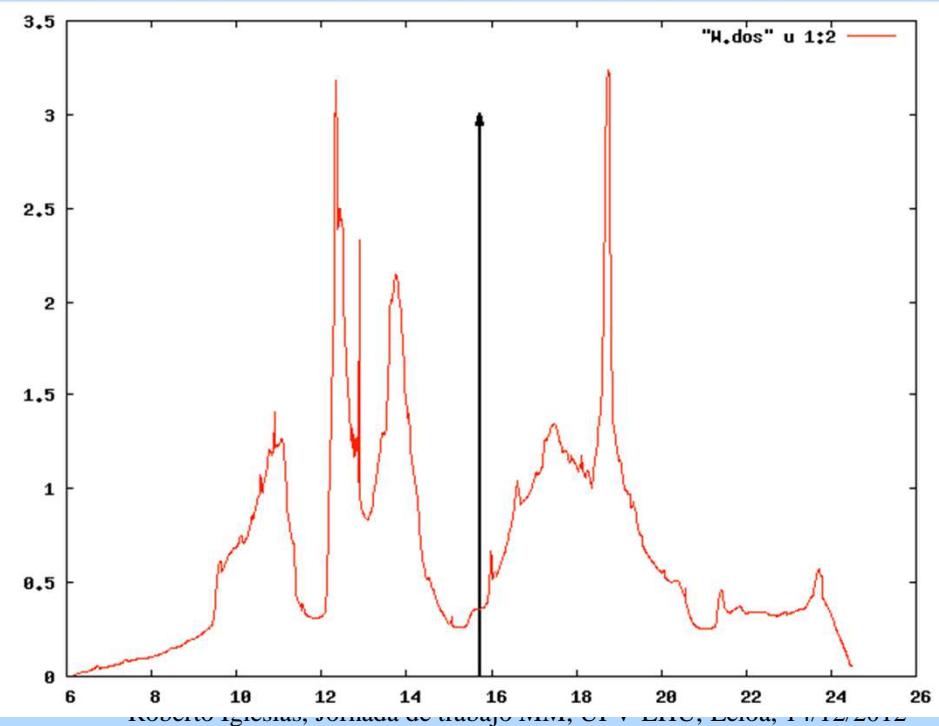
## W bulk, E vs. V curves





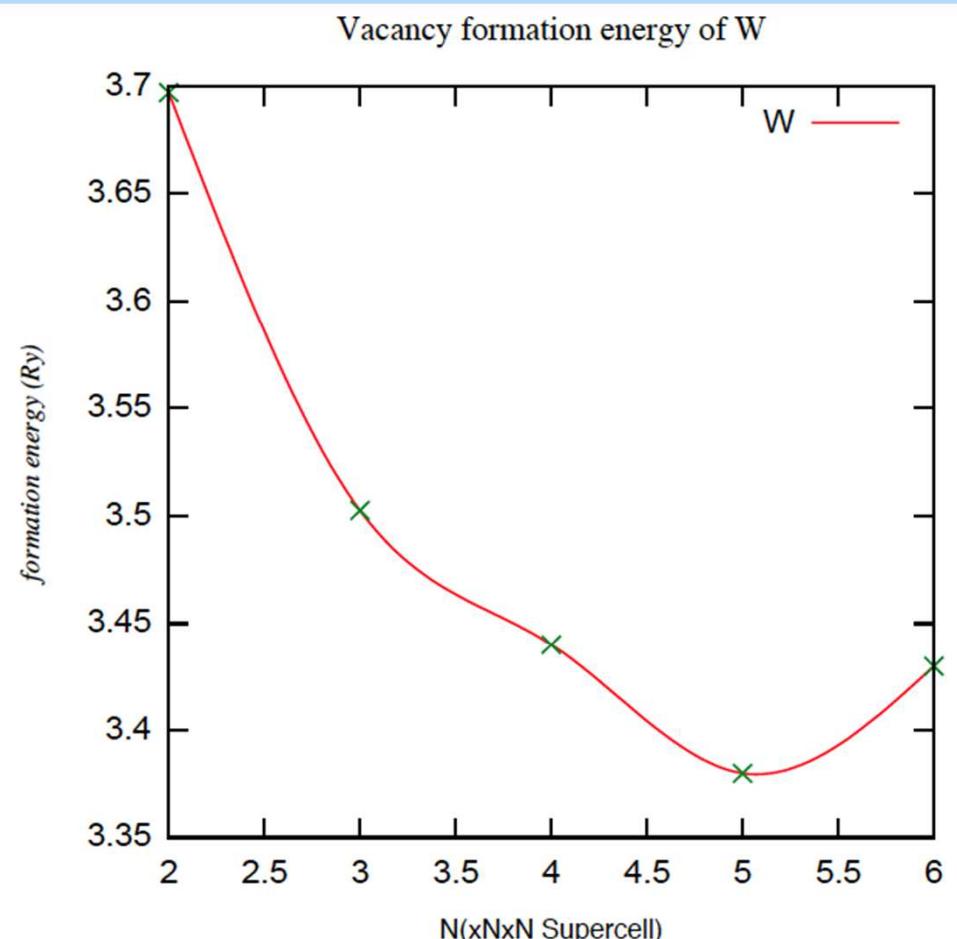
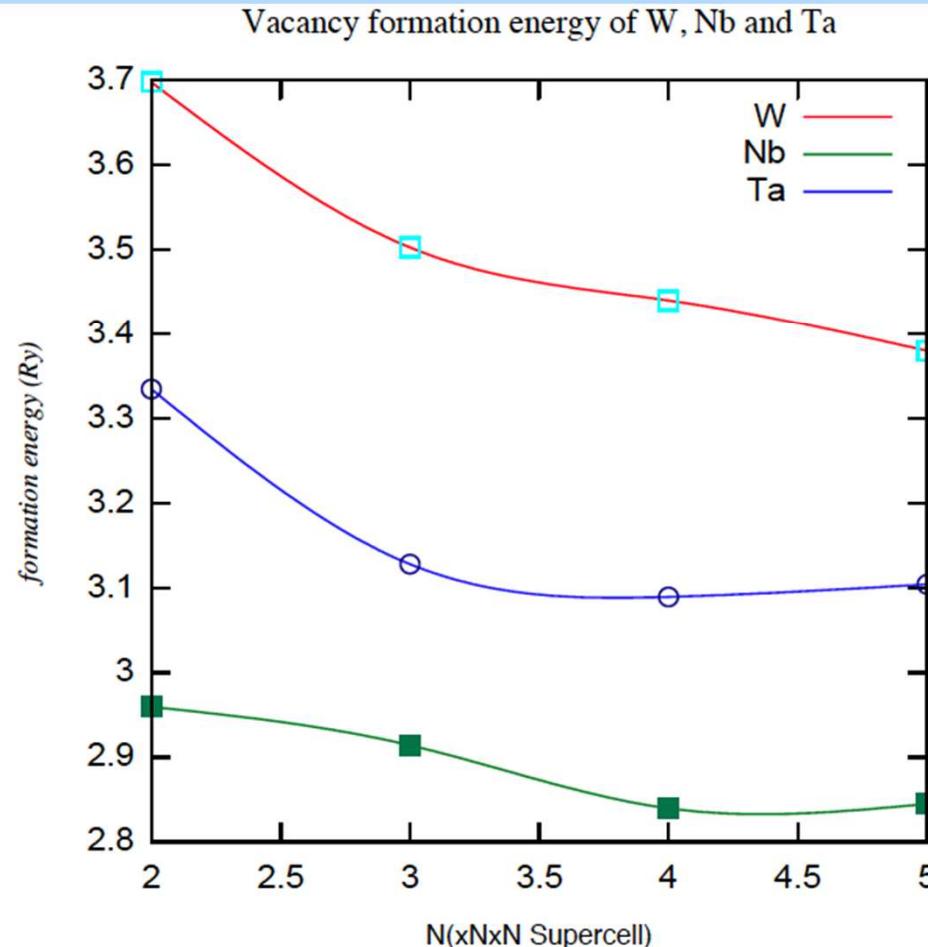
Wien2k

QE-PseudoP





# MonoV formation energies

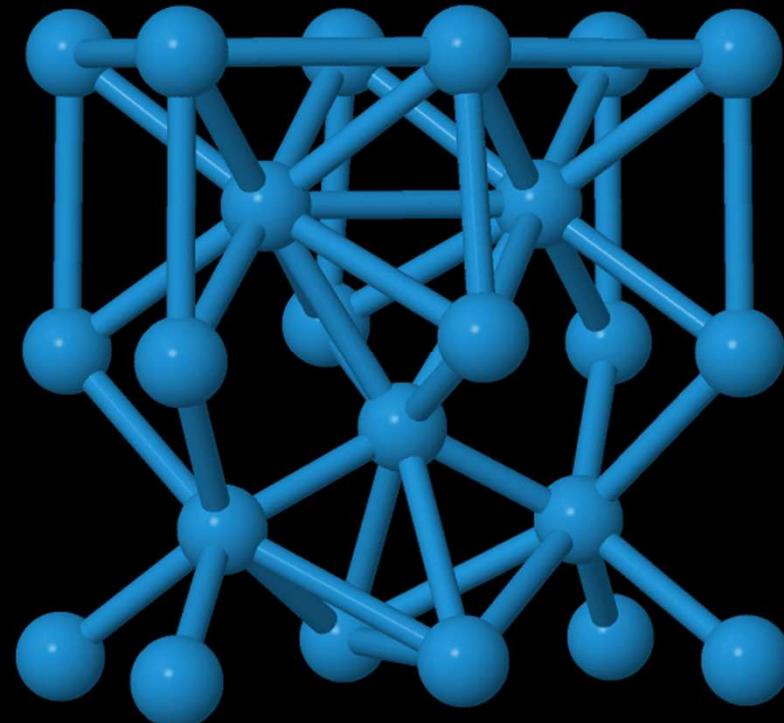


Fernández-Pello 2012



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[ AD FUTURUM ]

## Tetra to octa migration pathways in W

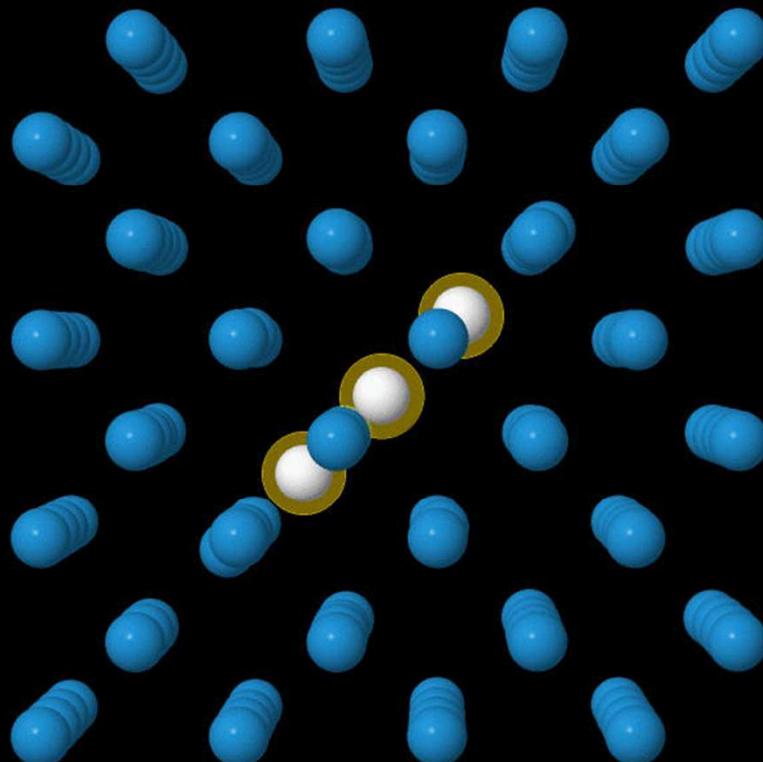


Jmol

González 2012

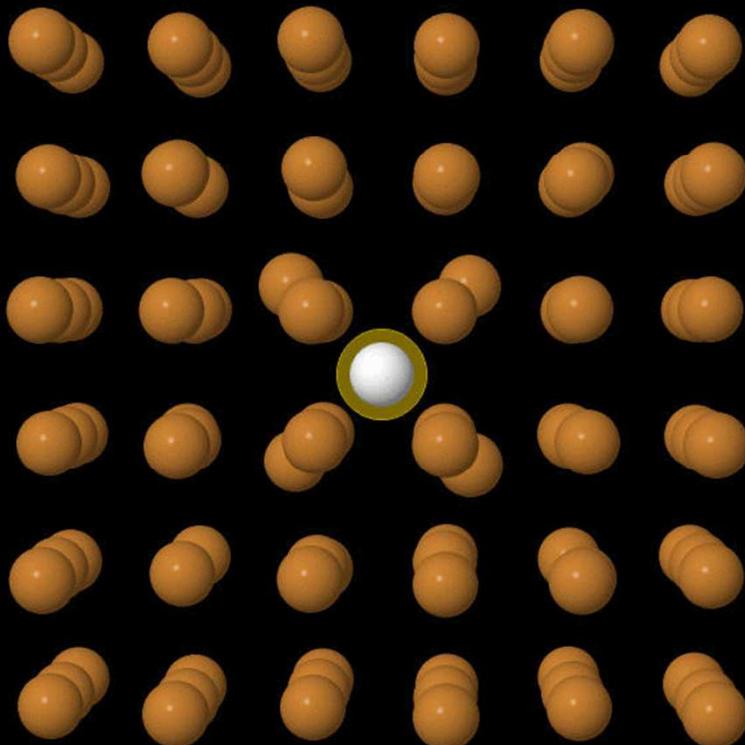


# Migración de una *dumbbell* [111] (W)



Jmol

González 2012

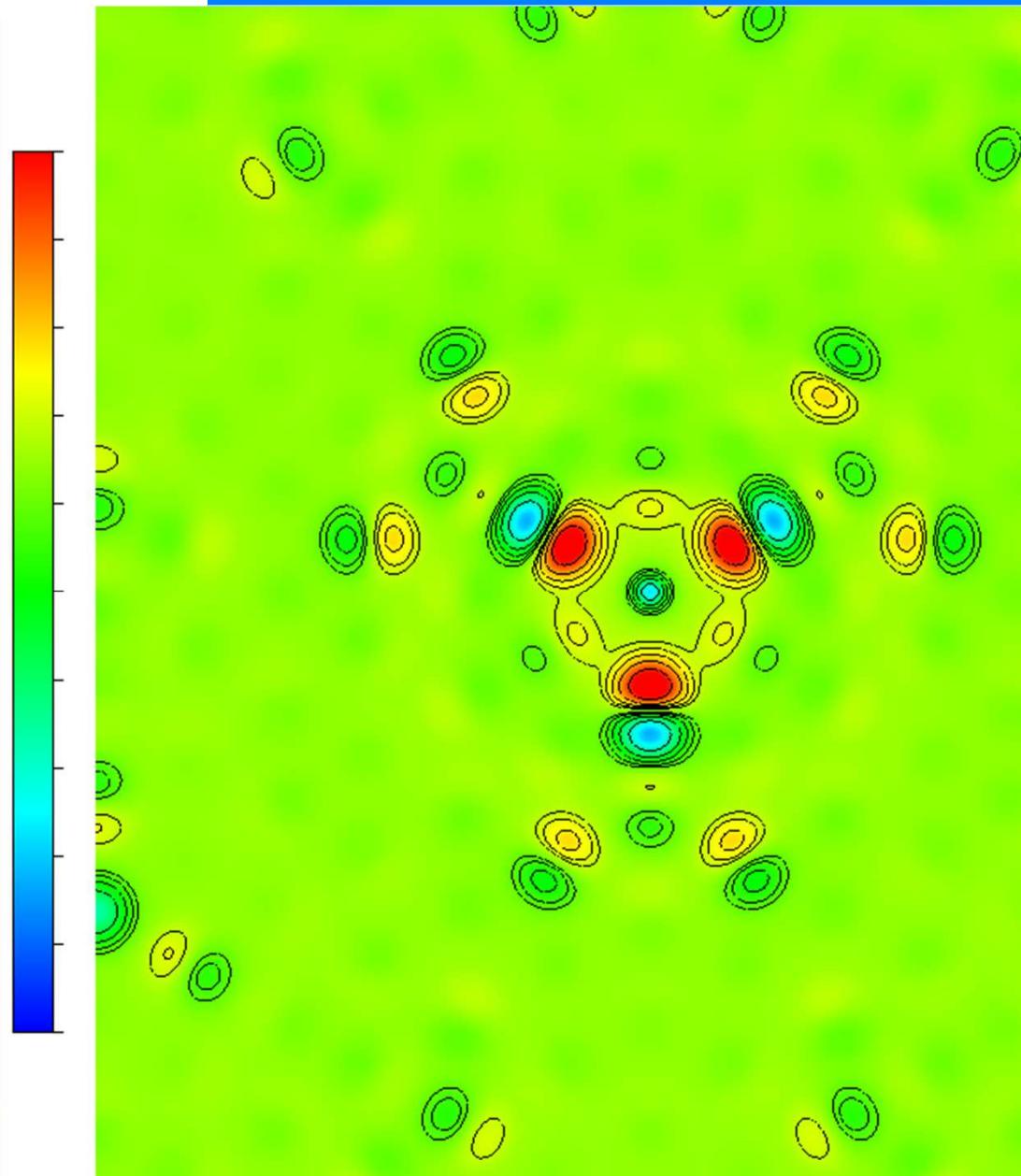


Jmol

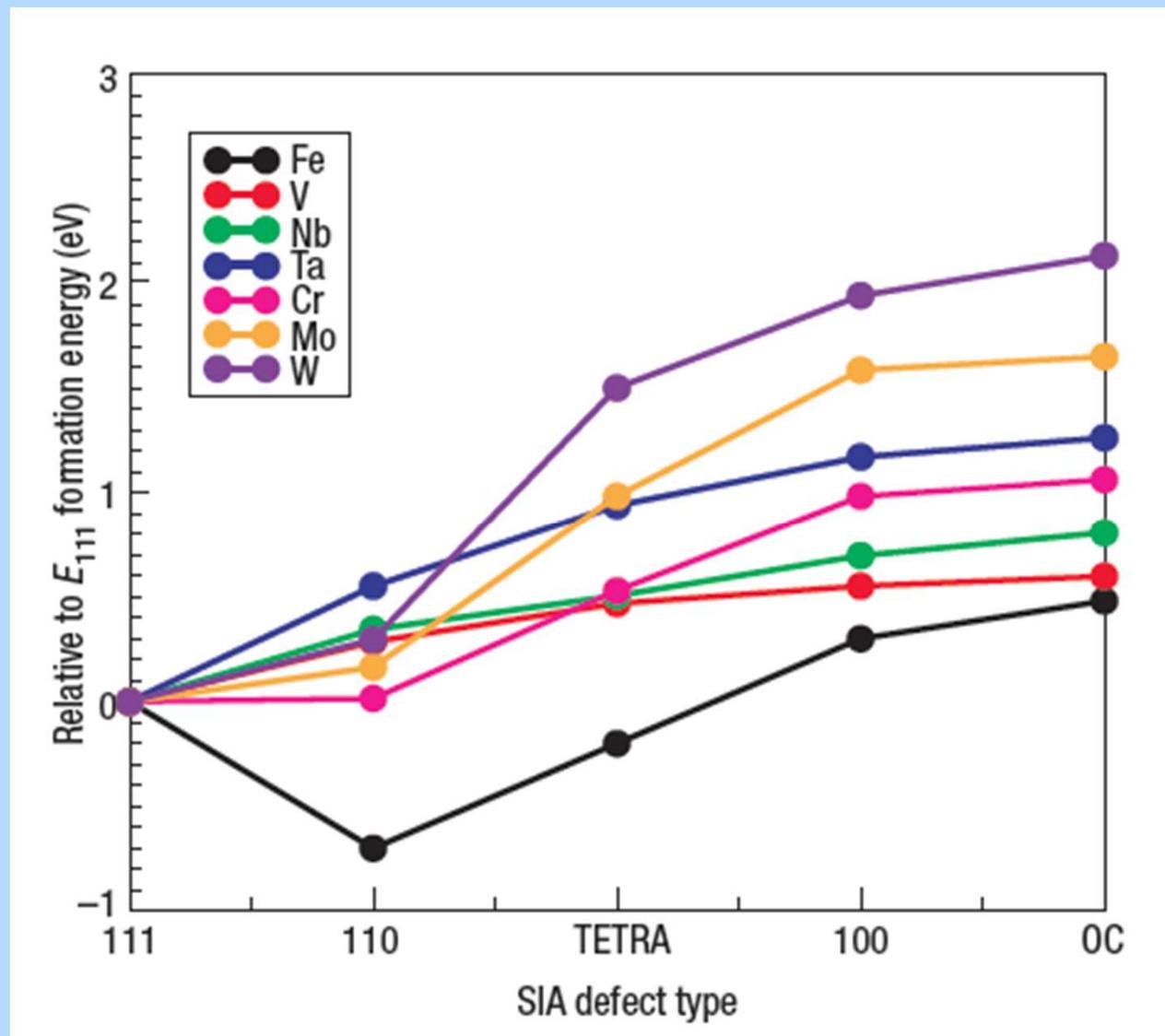
González 2012



# PbHe tetra charge density



Fraile 2012

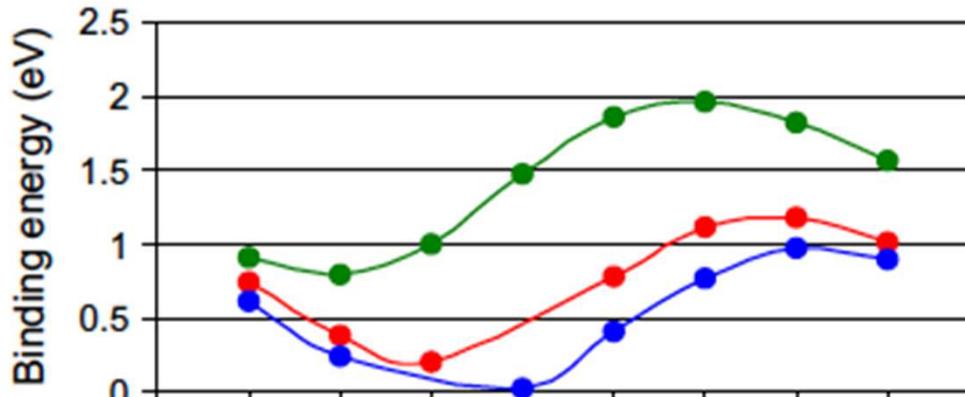
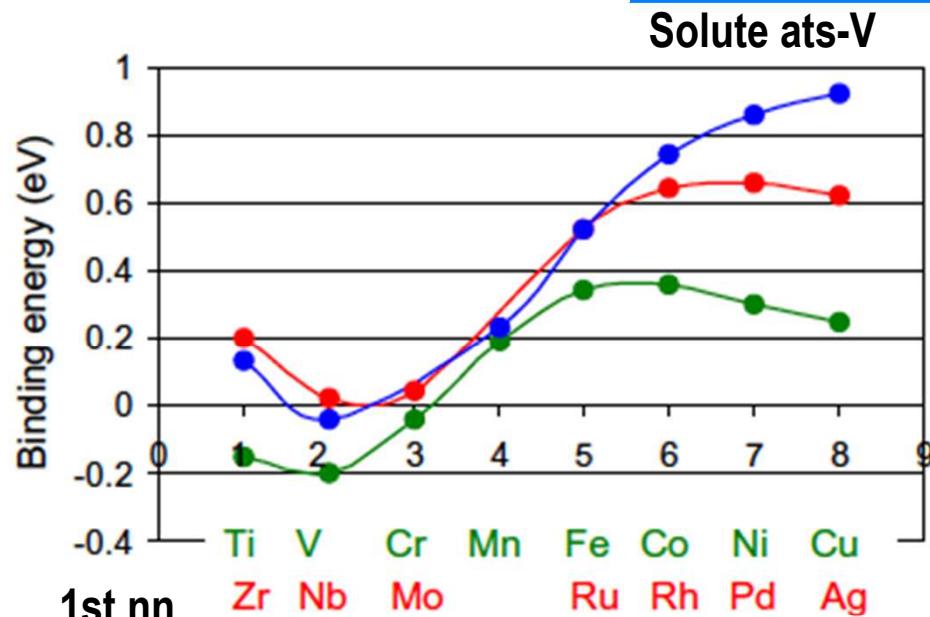


Nguyen-  
Manh 2006



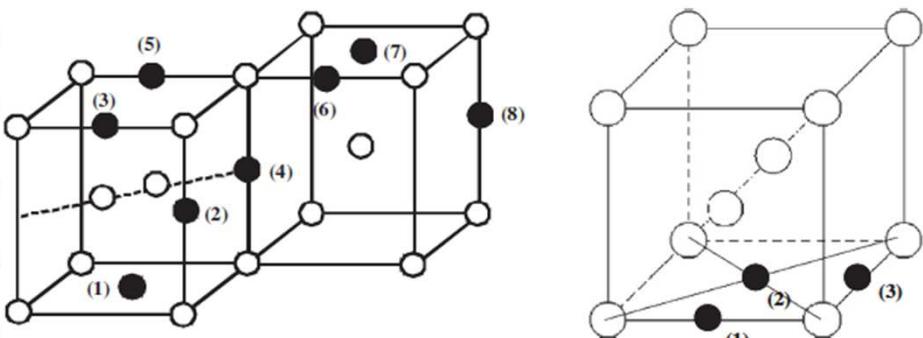
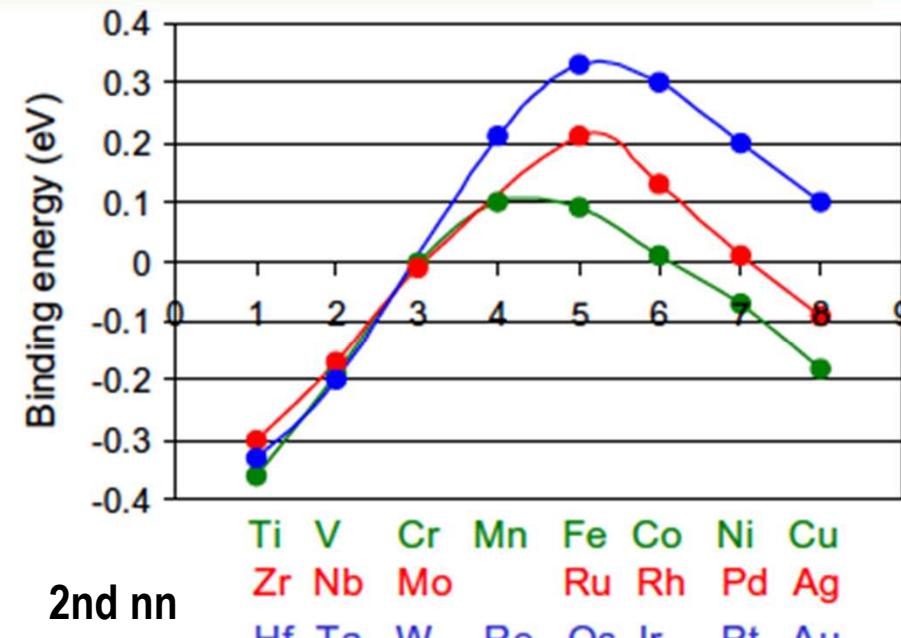
# Solute PD interactions in W

Becquart 2012



**Subs. TM ats-He**

Subs. TM	Ti	V	Cr	Mn	Fe	Co	Ni	Cu
Zr	0.90	0.75	0.65	0.70	0.20	0.10	0.15	0.10
Nb	0.85	0.40	0.30	0.25	0.20	0.15	0.10	0.15
Mo	0.80	0.20	0.15	0.20	0.10	0.05	0.10	0.15
W	1.50	0.80	0.70	0.80	0.40	0.30	0.40	0.45
Re	1.90	0.85	0.80	0.90	0.50	0.40	0.50	0.55
Os	1.95	1.15	1.10	1.00	0.70	0.60	0.70	0.75
Ir	1.80	1.20	1.15	1.05	0.90	0.80	0.90	0.95
Pt	1.55	1.10	1.05	1.00	0.95	0.85	0.95	1.00
Au	1.00	1.00	1.00	1.00	1.00	1.00	1.00	1.00

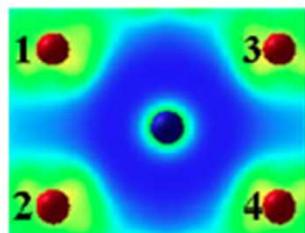
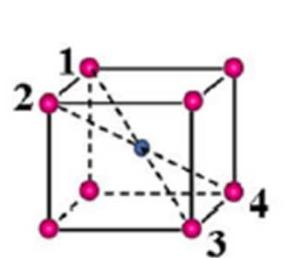


8 octahedral  
around  $\langle 110 \rangle$   
dumbbell

3 octahedral  
around  $\langle 111 \rangle$   
crowdion

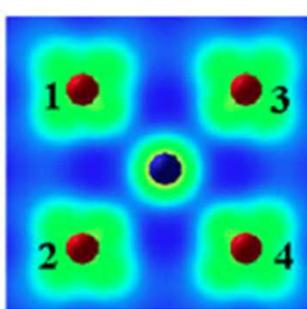
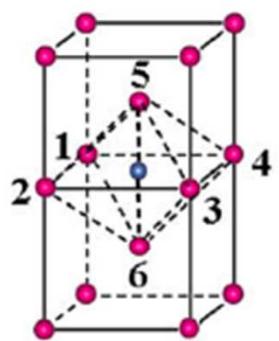


# H stability and diffusion in W

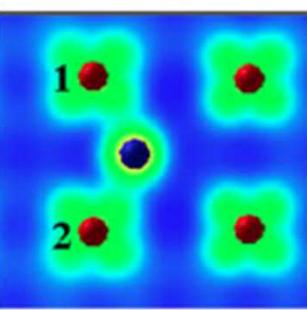
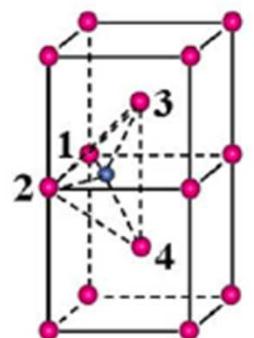


Tetrahedral site  
preferential

a



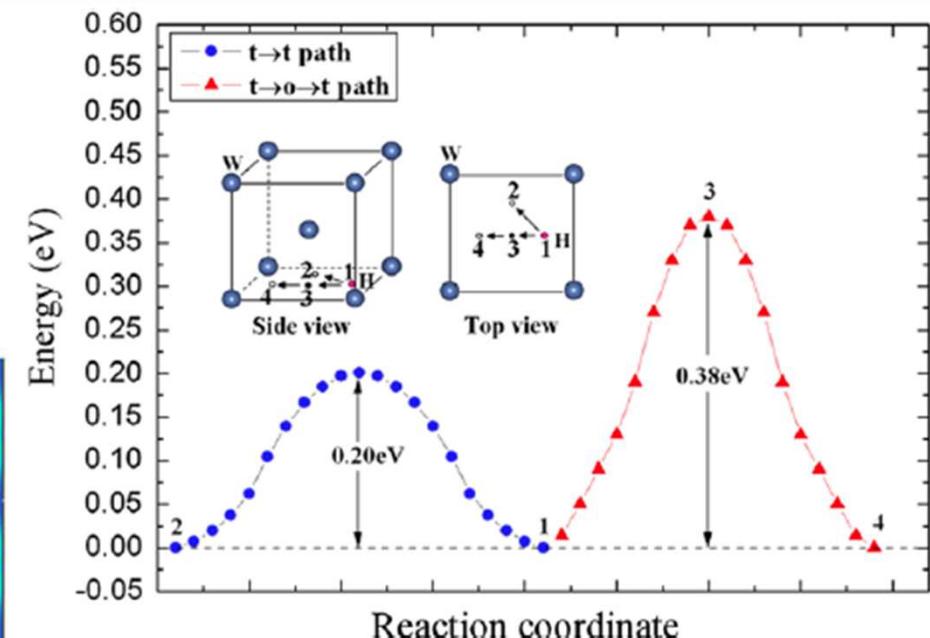
b



c

low ————— high

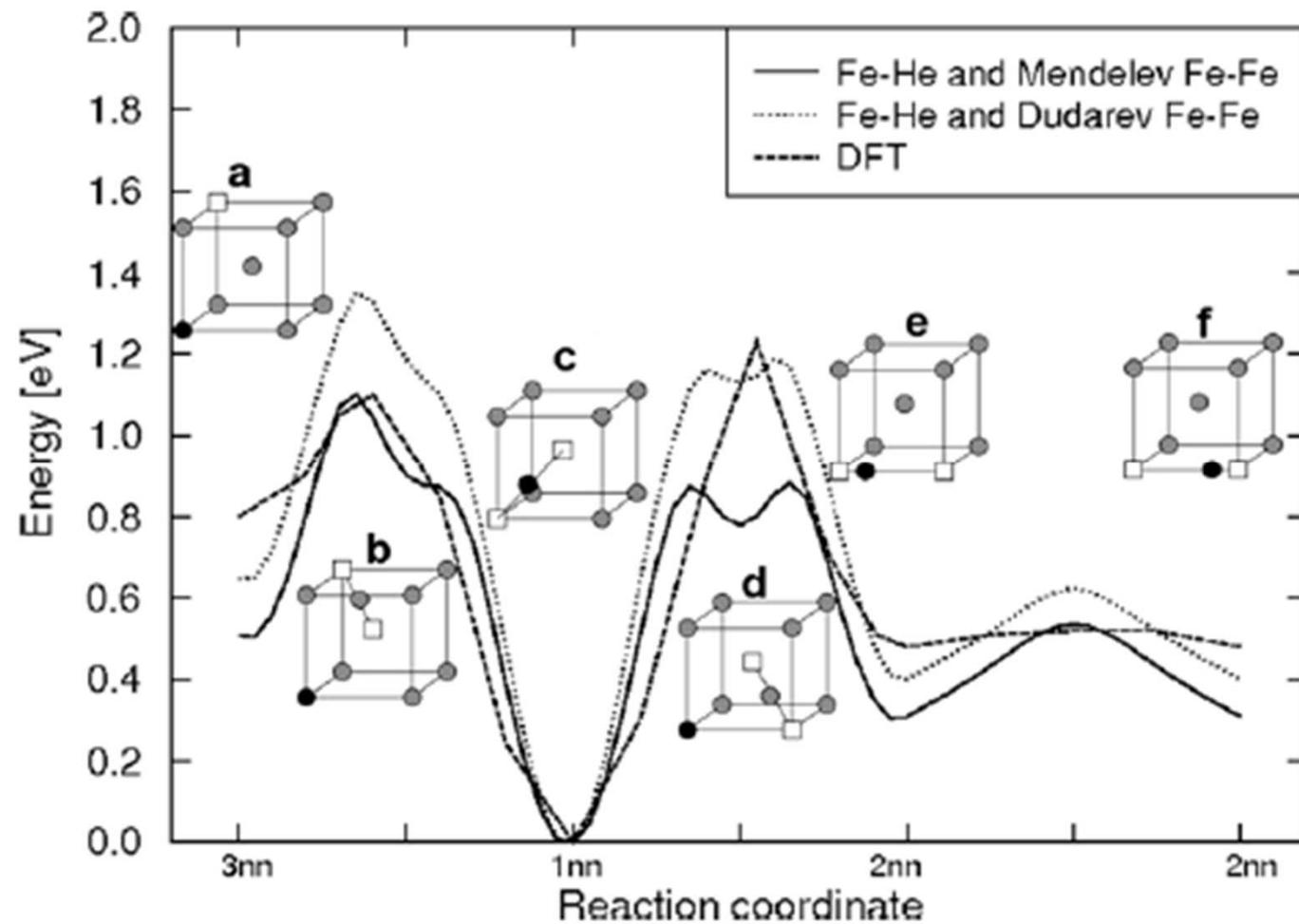
Charge density maps



Diffusion energy  
profile and  
paths

Liu 2009

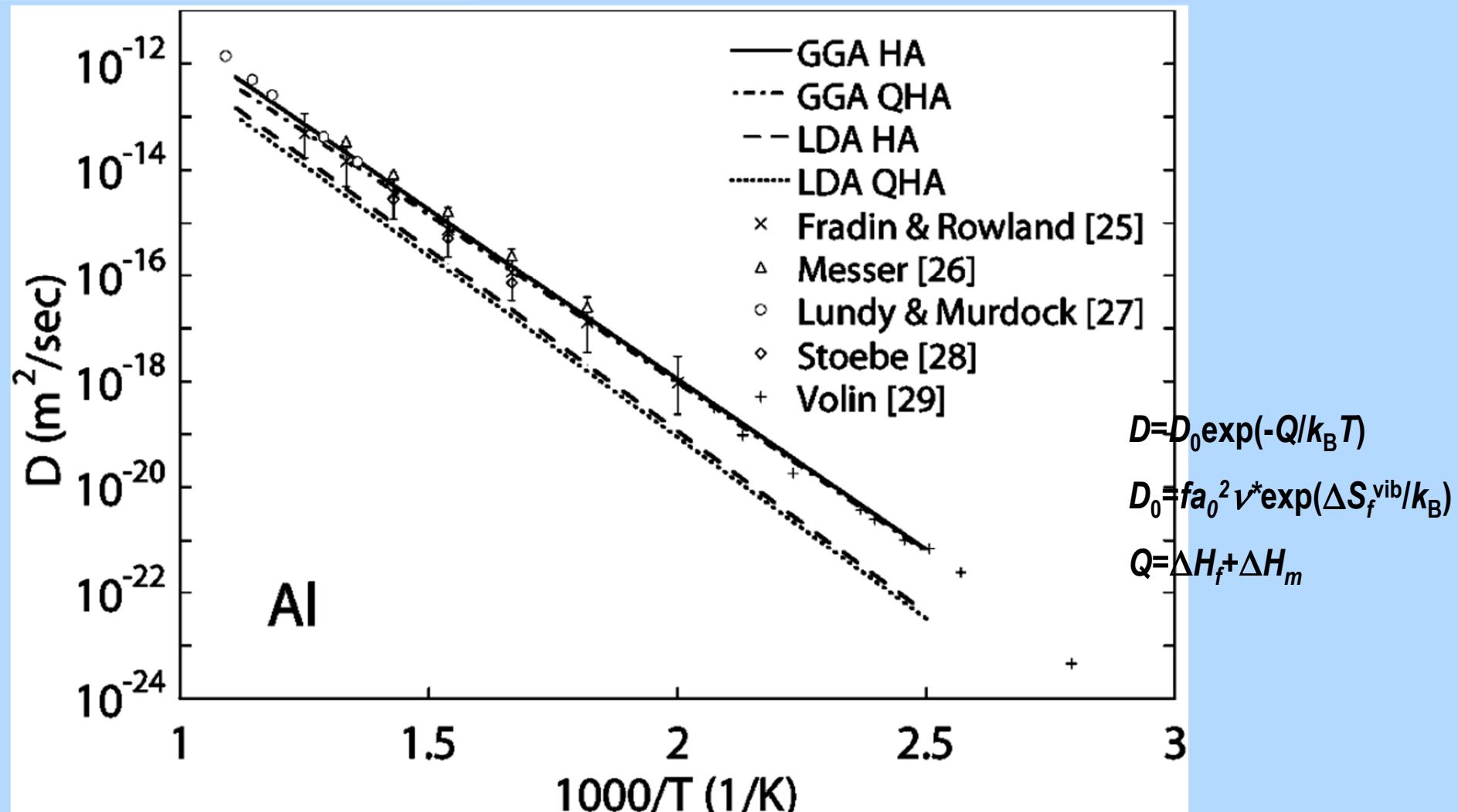
# Energy landscapes



Juslin 2008

HeV<sub>2</sub> complexes in Fe: MD with a new Fe-He pair potential

## Self-diffusion coefficients



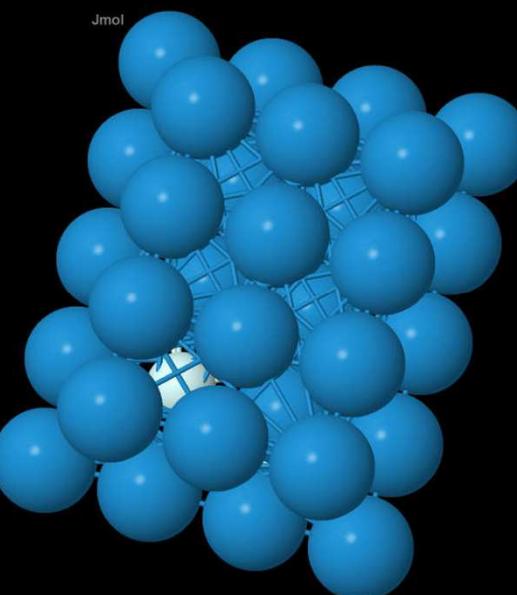
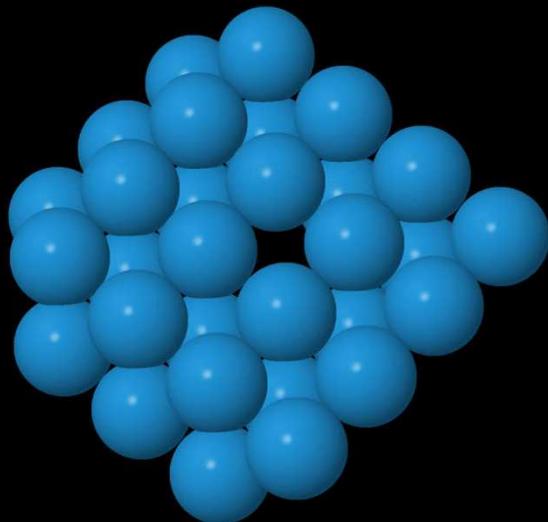
Arrhenius plot for Al: activation energy and diffusion prefactor using VASP

Mantina 2008



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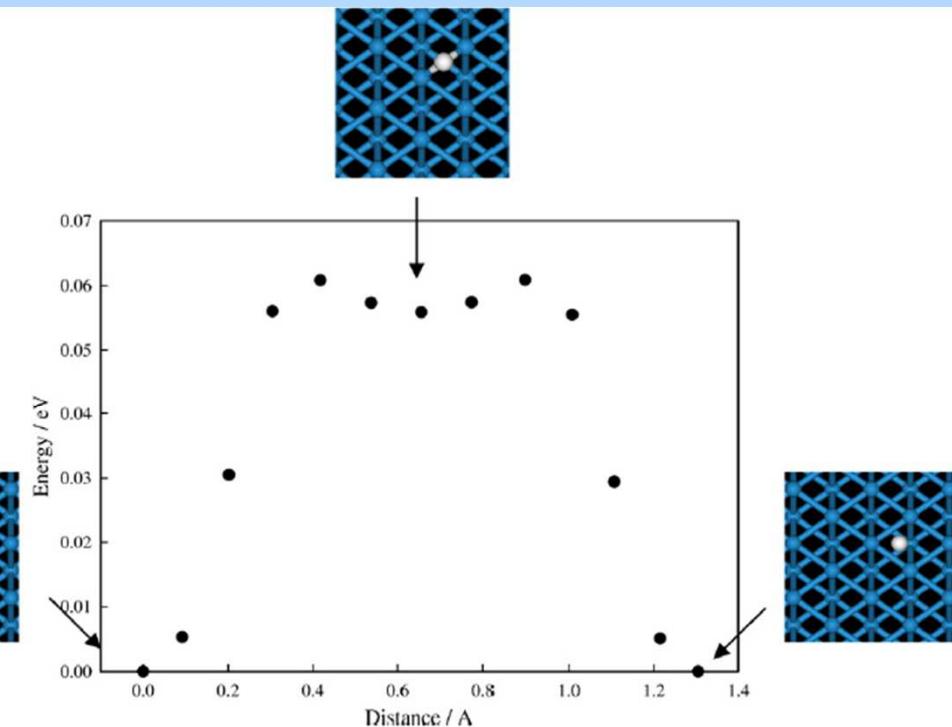
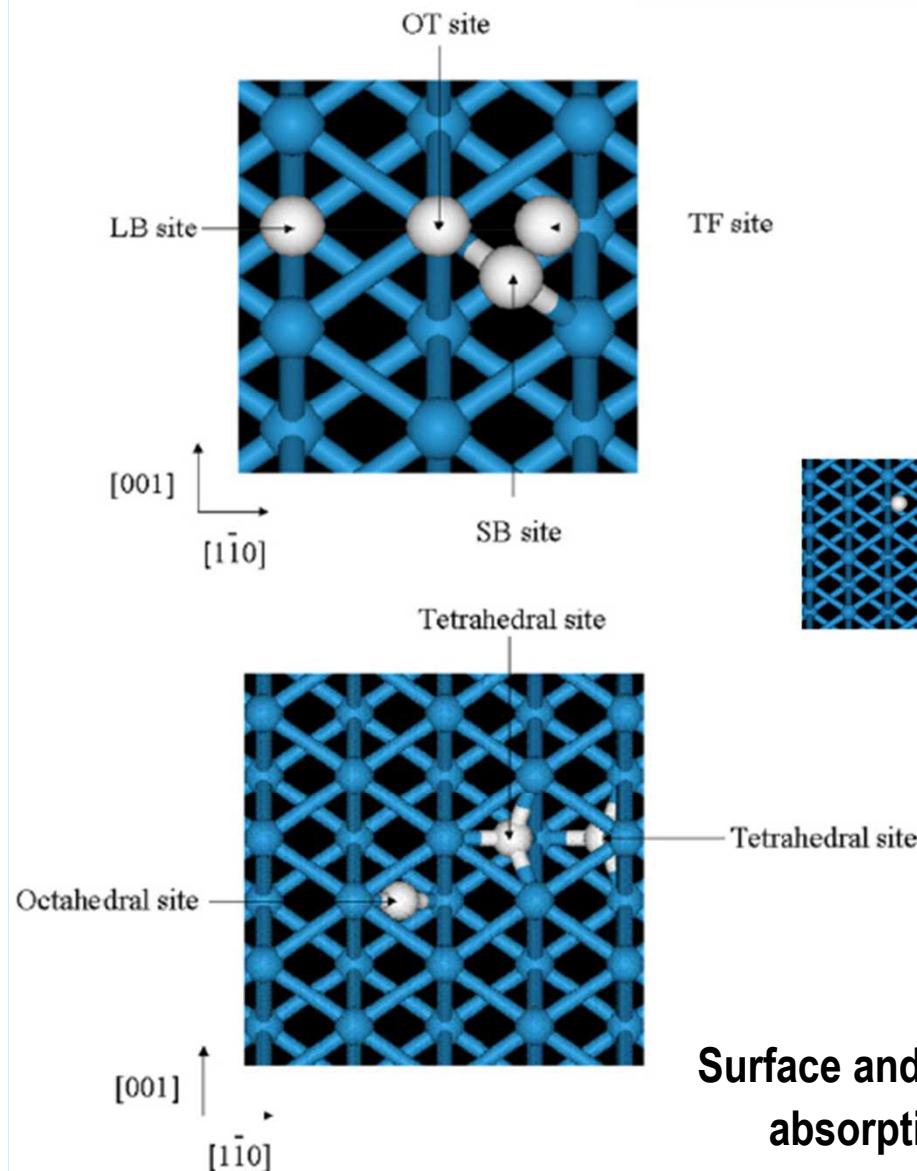
# Surfaces with vacancies and defects



Jmol



# H on W (110) surface

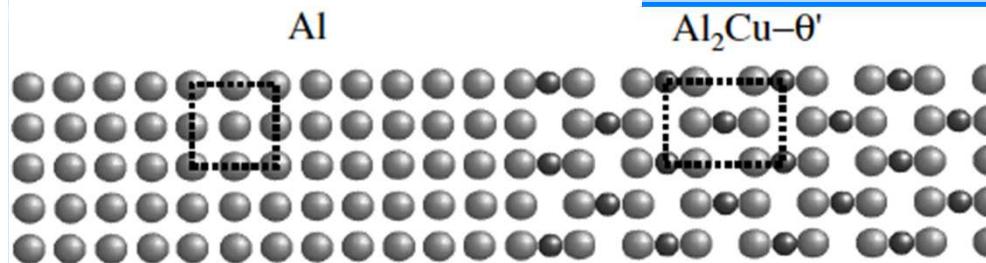


H diffusion potential energy curve on  
W (110) (1x1)-H surface

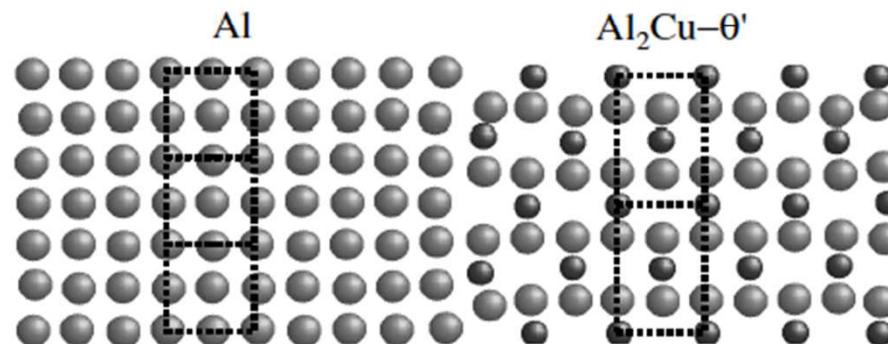
Surface and subsurface  
absorption sites

Nojima 2007

## IFs with DFT



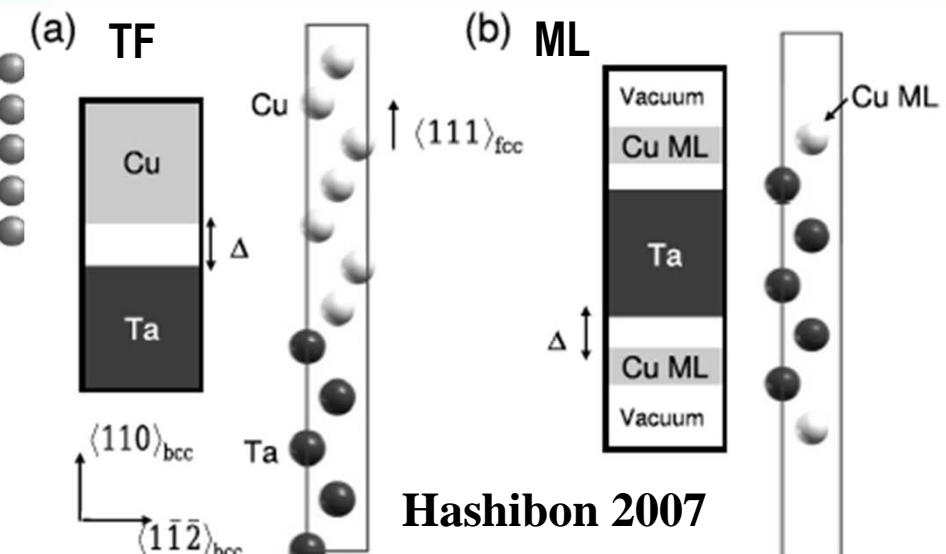
Vaithyanathan 2002 (a)



a) Coherent (100) IF

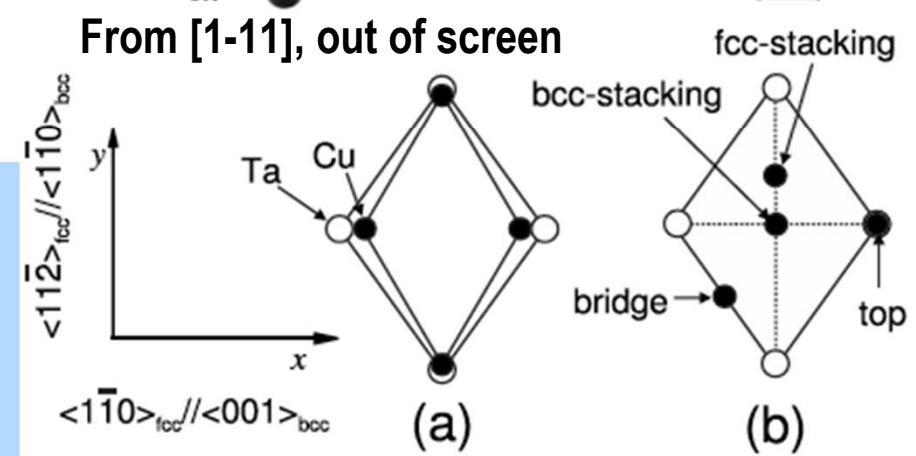
b) Semicoherent (001) IF

$\text{Al}_2\text{Cu}$  solid  
solution/Thin Cu film  
on Ta/  
 $\beta''\text{-Mg}_5\text{Si}_6/\alpha\text{-Al}$



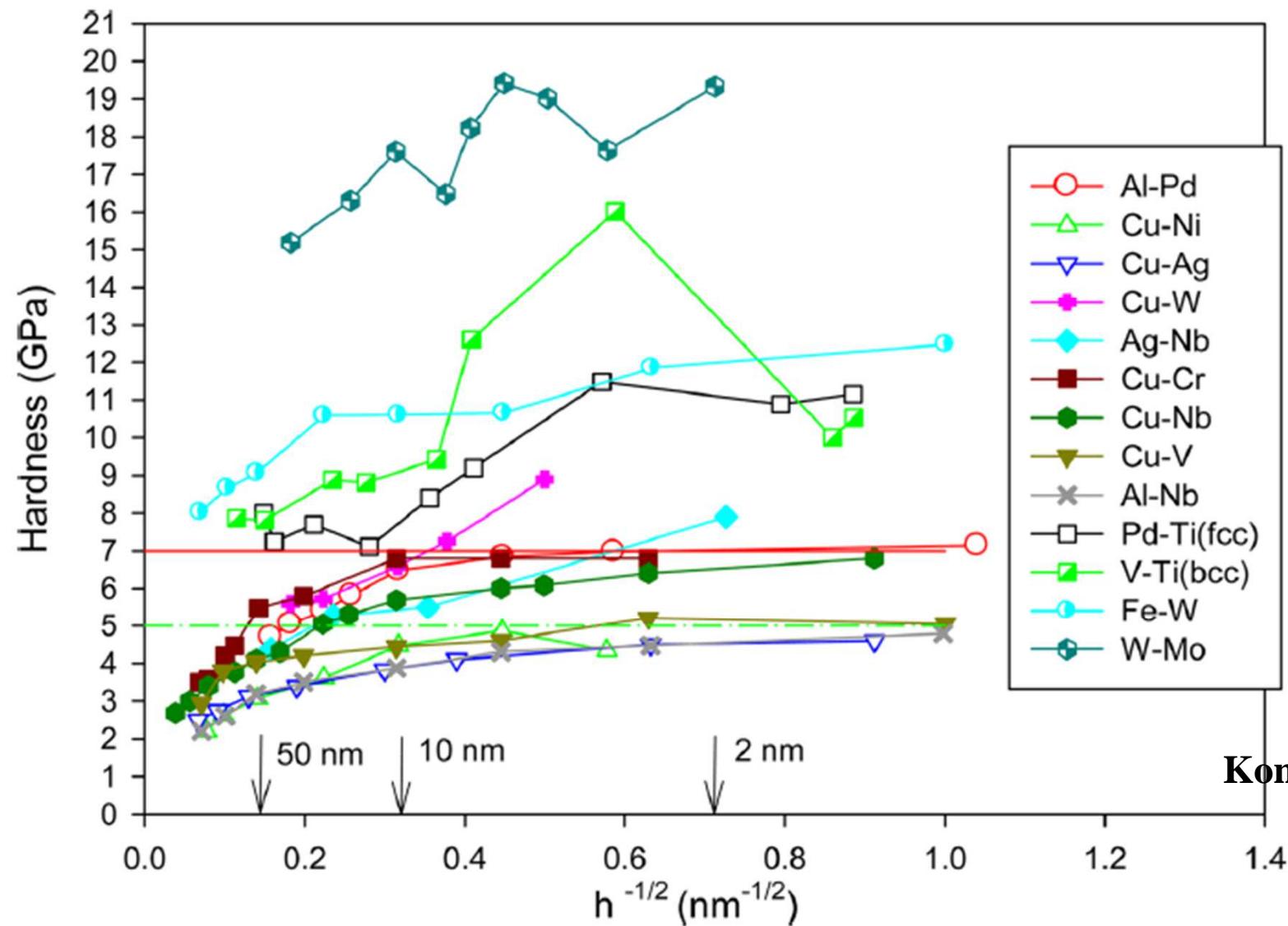
Hashibon 2007

From [1-11], out of screen



Incommensurate: one Commensurate cells: strained  
on top of each other Cu on unstrained Ta

# Strengthening in MLs with $\Delta H_f < 0$

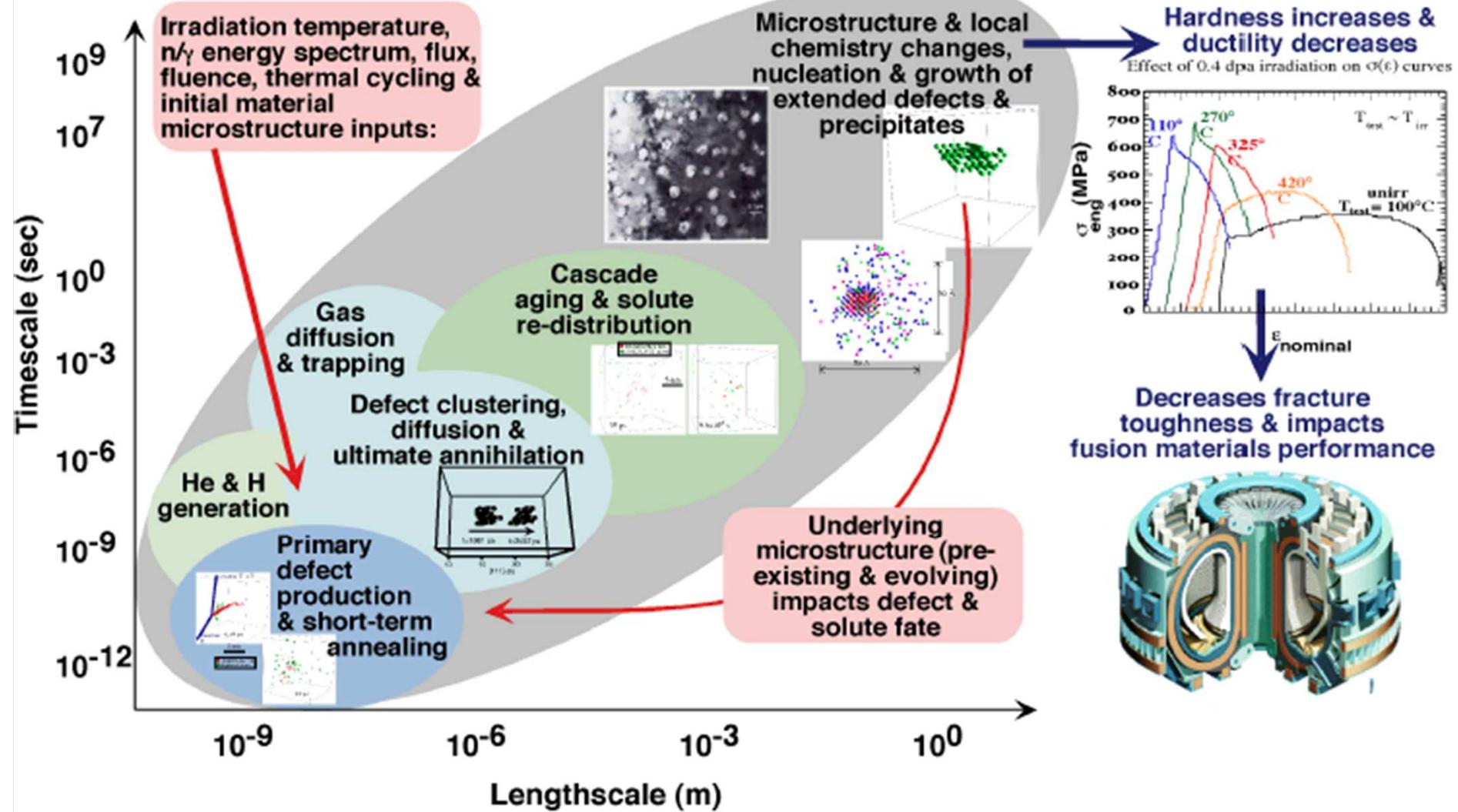


Kong 2011

Symbols: open, fcc/fcc; solid, fcc/bcc; half-filled, bcc/bcc

Roberto Iglesias, Jornada de trabajo MM, UPV-EHU, Leioa, 14/12/2012

# Procesos de daño por radiación



Cortesía de B. Wirth



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?

Darío

Sergio

Ángeles

Roberto

César